FINAL REPORT

on

ENGINEERING MODEL OF ANTENNA CAPACITANCE PROBE

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FINAL REPORT

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ENGINEERING MODEL OF ANTENNA CAPACITANCE PROBE

Contract No. NAS 5-9175

Prepared for:

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ABSTRACT

This report describes the development of the Engineering Model of the Antenna Capacitance Probe, part number 2158-R-434, which is the prototype of an instrument to be carried aboard the Radio Astronomy Explorer (RAE) Satellite in a forthcoming mission. The instrument is designed to measure the effective capacitance of the RAE antenna in two frequency ranges (750 kc and 1mc). Thus the capacitance not only can be determined directly, but also a function of frequency. The output to telemetry is binary digits rather than analog signals, hence the frequency as a function of capacitance has a high degree of accuracy.

The expected radiation dosage influenced the selection of the semiconductors and the circuit design was based on $h_{\rm FE}$ derating to insure operation should higher dosage be encountered. If further longevity is desired, certain transistor substitution is suggested based on subsequent information and investigation.

An overall system operation is followed by a detailed operation of the individual circuit explanation, including the appropriate waveforms.

A detailed reliability and failure analysis shows that the probability of complete success is .956 and the probability of complete failure is .044.

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I. INTRODUCTION

This report describes the Englanding Model of the Capacitance Probe produced under Contract NAS 5-3759. This Capacitance Probe, is the prototype of an insturment to be surried aboard the Radio Astronomy Explorer (RAE) Satellite in a forthcoming mission. The purpose of the probe is to measure the capacitance which occurs between each of two antenna booms connected as dipoles, and the spacecraft skin. The antenna capacitance will be measured at two frequencies widely separated from each other. The instrument is designed as the RAE Antenna Capacitance Probe part number 2158-R-434.

The basic principle of measurement of the Capacitance Probe consists in reflecting the capacitance which exists between the two antenna booms, and the spacecraft skin to an oscillator which will change its operating frequency in direct proportion to the capacitance seen by the antennas. Each antenna boom is fed by a coaxial cable, and in order for these booms to look like a dipole antenna which is balanced to ground from each boom, some sort of impedance matching device is necessary. For this reason balun transformers are used in the oscillator circuit, the secondary of which acts as part of the tuned circuit of the oscillator. Since capacitance is a function of frequency, two oscillators are used, so that capacitance as a function of frequency can also be determined.

A plot of capacitance versus oscillator frequency is provided for each oscillator. Prior to launch the capacitance of the antenna base, coaxial cable,

and the oscillator capacitance can be determined. Thus by subtracting out this total predetermined capacitance from the capacitance as measured by the oscillator the antenna capacitance can be determined.

Each oscillator is completely enclosed in a metal container which is temperature monitored. In addition, a calibrating capacitor is provided so that oscillator drift can be detected if it occurs and the readings compensated for. The overall system then produces frequencies which are directly related to the low frequency calibrate capacitance, high frequency capacitance, the antenna low frequency, and the antenna high frequency. These frequencies are then telemetered to ground so that a record is obtained of the antenna capacitance during flight.

The power to the Capacitance Probe will be turned off and on during the flight. This will reduce the power consumption and eliminate interference problems between other experiments.

II. SYSTEM OPERATION

The general principle of operation of the Antenna Capacitance Probe has already been outlined in Section I above. This will now be extended by a more detailed functional description of the instrument, which will be followed by a discussion of the theory of operation of the system. Detailed description of some of the circuits will be presented in section IV.

2.1 GENERAL SYSTEM OPERATION

A block diagram of the Antenna Capacitance Probe is shown in Figure

1. The experiment is run synchronously from the 400 cps spacecraft clock.

Upon receiving the power to the experiment, a minimum of 2.5 seconds is required for oscillator stability. At some time thereafter the programmer can initiate the accumulate or read command, which arrives as a pulse shifting from +6 volts (off) to 0 volts (on). The Capacitance probe, upon receipt of this command clears the counter, shift register and control circuitry by using this accumulate pulse as a reset.

Once the experiment is reset the oscillator frequencies are gated to the counter. The sequence of the frequencies going to the counter are: low frequency calibrate; 750 kcs; high frequency calibrate, 1 mcps; antenna low frequency; antenna high frequency. This sequence is internally controlled from the control logic circuitry by use of OR and NAND gates. The output of the oscillators are shaped for counter triggering by the squaring circuitry.

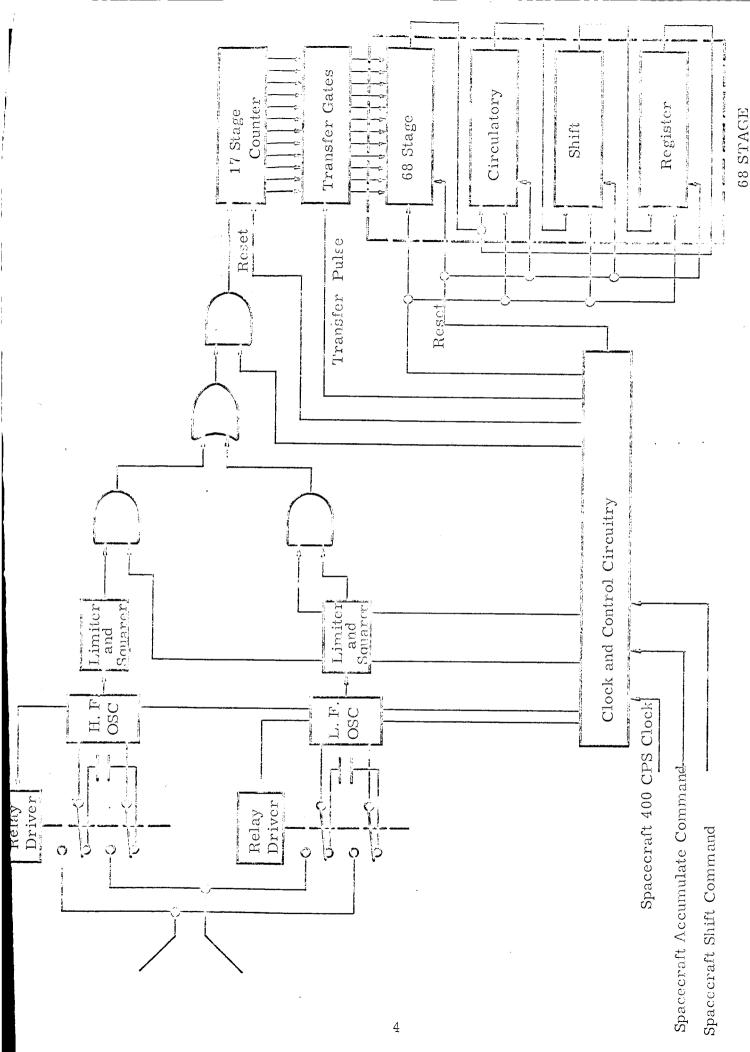


Figure 1, 1-Block Diagram Antenna Capacitance Probe

After each input to the counter which lasts exactly for 100 milliseconds, the counter input is temporarily disabled while the parallel
transfer of information from the counter to the shift register is made and
the counter is reset. The counter then accepts the next frequency. During
this count time the information in the shift register is serially shifted down
17 stages to make room for the following parallel transfer to the shift register.

After four inputs to the counter, which requires 480 milliseconds, the shift register is full and the control circuitry will allow it to accept no more information, by disabling the transfer and shift pulse lines.

The information now contained in the shift register in binary digits is ready to be sent to telemetry upon receipt of the Shift Command. Some convenient period of time after the 480 milliseconds required to fill the register, the shift command will occur in the form of a gating pulse to a NAND gate, shifting from a off-state potential of +6 V to a on potential of zero volts and lasting for at least some integal multiple of 168.75 milliseconds. This is to allow 68 pulses from the 400 cps spacecraft clock pulse, which is the other input of the NAND gate, to shift the information from the register out to telemetry. Since this is a non-distruct circulatory type of shift register, at the end of the 68th pulse the information will have been completely shifted out, but also will be repositioned in the register identically to its position before the arrival of the shift command.

The information to telemetry is in the form of binary digits rather than analog signals, thus enabling each bit of frequency to be read. However some bit may be dropped or lost due to noise in transmission and for this reason it may be desirable to shift the information out twice, since no parity code has been provided.

Upon the completion of the shift pulse, when all the information stored in the register has been sent to telemetry the programmer may shut off the power to the Capacitance Probe, and the antennas can now be time shared with another experiment.

III. RADIATION EFFECTS ANALYSIS

3.1 INTRODUCTION

The requirement for radiation hardening is due to the fact that the RAE Satellite is to be flown in an orbit lying in the Van Allen belt. This is a circular orbit at an abitude of 8000 km inclined 50° to the equator. Because the intended service life of the satellite is at least one year, this means that the instruments will be in a radiation environment for 10,000 hours or more. Electronic components, such as resistors, capacitors, coils and insulators having been tested repeatedly in various radiation environments, have shown that they are orders of magnitudes less sensitive to radiation than most semiconductors. Therefore, it is reasonable to conclude that the maximum radiation tolerant level, that is the threshold failure, will be primarily determined by the semiconductors, In addition, the circuit design based on reduced gain will have a direct bearing on circuit failure due to radiation dosage. Since semiconductor devices are the most sensitive components to space radiation, this analysis is limited to the semiconductor devices of the Capacitor Probe.

3.2 TYPE OF NUCLEAR RADIATION EXPECTED

A combination of nuclear radiation environment may be encountered by a space vehicle passing through the Van Allen belts. Some of the types of radiation are, the steady state trapped radiation, cosmic radiation, auroral radiation and solor flare radiation. The greatest electronic failure damage to space electronic system in earth orbit is due to trapped particles which are the Van Allen electrons

and protons plus the Starfish explosion. Although the Starfish electron levels at the higher altitudes have not decayed as quickly, the electron levels in the lower portion of the electron belt have decayed by approximately an order of magnitude.

Cosmic radiation consist mainly of hydrogen nuclear (protons) having very high speed and whose energy is in the range of 1 x 10^9 to 1 x 10^{10} electron volts. It is impractical to shield against cosmic particles of such great penetration.

Since the cosmic-particle flux is roughly about two particles per square centimeter per second. The ionization dose rate which can be attributed to cosmic radiation is in the vicinity of 10⁻⁴ rads per hour and that attributable to secondarily produced particles is about 10⁻³ rads per hour. Most materials and electronic components are uneffected until an ionization dose of 10⁻⁴ rads has been absorbed. Consequently cosmic radiation does not pose a severe threat to the performance of electronic equipment, especially when the materials and packaging are such as to reduce the secondary radiation or ionization effects. That is, complete potting of package to reduce any air space, and the restriction of materials such as teflon, Kel-F and the like. Although certain amounts of radiation effects can be annealed out by subjecting the electronic components to high temperatures, the temperature environment of the spacecraft is for too low for any efficient annealing to take place.

The innear Van Allen belt beginning somewhere between 399 to 1199 kilometers depending upon the latitude, and extending from about 45° north magnetic latitude

to 45° south magnetic latitude is made up mainly of a large number of electrons and protons of various kinetic energies all trapped by the earth's magnetic field.

Since radiation energy may be supplied in two forms: electromagnetic radiation, such as X- and gamma rays; or as particle radiation. The particles comprising the second basic form of radiation energy can be positively charged protons, negatively charged electrons or uncharged neutrons which are moving at speeds slower than that of light.

For charged particles, the interaction between the particle and an atom of the struck material produces a displacement which is caused by the electrostatic force between the nuclear charge and the moving particle. This displacement will occur if the charge particle has sufficient energy and if it passes within the radius of the inner most electron orbit. Uncharged particles such as neutrons, however, must pass within the much smaller radius of the atomic nucleus. If electrons have sufficent kinetic energy that is energies greater than 200 kev, they will create displacement. Since electrons of energies greater than 200 kev comprise less than 10% of the total in the Van Allen belts, displacements by electrons are not a major concern. However, whether the electrons originate in the Van Allen belt or as secondary electrons produced by gamma radiation they create the same effect.

Secondary electrons produced by gamma radiation processes can attain energies in excess of 200 kev. For primary electrons with energies ranging from 40 to 50 million electron volts, the energy is expended in the form of braking radiation, which is a complete conversion from the electron into gamma radiation. The threat from electrons in space radiation environment is due more from

Although the average energy of electrons in the belt allows shielding, the secondary radiations they create is more troublesome. Protons are the most penetrating type of charged particle radiation in the Van Allen belts because of their higher average energy and their larger mass. Shielding against protons, therefore is difficult.

3.3 RADIATION ESTIMATES

Due to the spacecrafts orbit it has been estimated that the radiation dosage will be: 2.2×10^{12} electrons per cm² per year having kinetic energies greater than .5 mev; and 10^4 protons per cm² per second having kinetic energies greater than 30 mev. Further, it has been estimated that the spacecraft will provide a shielding density of .63 grams per cm² and the package will provide a shielding of .4 grams per cm². If it is assumed that this shielding will be done with aluminum then all the constant troublesome radiation effects will be due totally to protons having kinetic energies greater than 20 mev, as the shielding will be sufficient to effectively shield against all but the most energetic electrons (3 mev)³.

Definite conclusions and expectations concerning nuclear radiation damage are not possible at this time, due partly to insufficient investigations, results and methods which are not totally compatible. Although it is well known that the radiation resistance of semiconductors can vary between batch lots of the same type for any given manufacturer it has also been generally agreed that some methods

of manufacturers are better than others for reducing failure due to nuclear radiation. Germaniun it would seem is better in general than sicilon, however, trade-offs exist when the circuit use is considered.

Although the transistors selected for use in the Capacitance Probe do not necessarily represent ones having the highest possible radiation resistant characteristics; they were chosen consistent with the current available information as to preferred type, previous performance, and radiation testing results. They

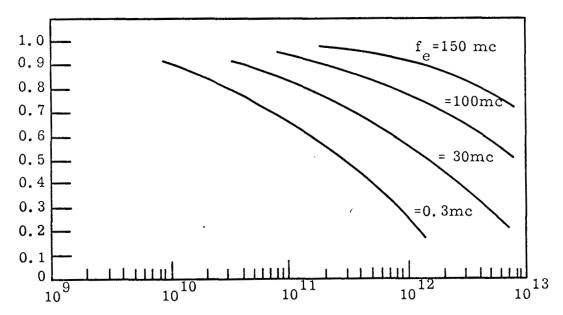


Figure 3. 1-NEUTRON EXPOSURE (NVT, E >.1MEV)

are of the high f_T and low breakdown voltage type. The low breakdown voltage is also a requirement in the design of other radiation tolerant semiconductor devices, namely diodes. Semiconductor radiation dosage in laboratory testing have, because of convience, been exposed mainly to neutrons rather than electrons or protons, therfore in order to reduce all data to common terms, the proton and electron rates can be reduced to equivalent neutron dose rates. For protons the average figure which can be used for a close equivalence is to multiply the proton

rate by 4.2; for electrons, multiply the rate by 0.01 in order to get the equivalent neutron rate.

The susceptibility of transistors to radiation is a function of the transit time across the base region and, thus is a function of the transistor alpha cut-off frequency. Degradation in transistor alpha as a function of neutron flux for various alpha cutoff transistors is shown in Figure 3.1. By converting the expected dosage of electrons and protons to equivalent total dosage of neutrons, the expected dosage would be 11.2×10^4 neutrons per square cm per second.

The alpha cutoff frequency of the 2N930 is 30 Mc. From Figure 3.1 a total dose of 41 x 10¹¹ n/cm² would be required for the alpha to decrease to a value 0.7 of its initial value, which means that if no derating is done in the circuit design, the 2N930 could remain in orbit 1.16 years before its alpha degrades to 0.7 of its initial value. Actually in every discrete circuit of the Capacitance Probe the circuits have been designed to work with the common emitter gain lower than 0.5. The alpha cutoff frequency of the 2N2604 and 2N915 are 100 Mc and 400 Mc respectively and therefore have greater lifetimes than the 2N930.

An effective increase in the lifetime can be obtained by the substitution of 2N918 transistor for the 2N929 and 2N930, and substituting 2N3251 for the 2N871. This would mean that the lowest alpha would be 200 Mc; that is, the life would be extended to better than 8.3 years before the lowest alpha cutoff transistor would be degraded to 0.7 of its original value.

Similarily, the selection of the inegrated circuits used in the Capacitance Probe are those whose past performance in space and radiation test results indicate that they would survive the expected exposure in the Van Allen belt. There have not been many studies performed in integrated circuits since they are relatively new. However, those which have been performed conclude that the integrated circuits will be as radiation resistant as the same circuit makeup with compatible discrete components. Those Texas Instrument (series 51) circuits which were tested showed that first failures occured at about 1.8 x 10^{14} n/cm² which is an order of magnitude above that discussed above. One possible means of improving the radiation resistance of these units, which could easily be incorporated in later units if deemed necessary, would be to decrease fanout loading, since it has been found that there is a direct correlation between fanout and failure dosage.

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IV. CIRCUIT DESCRIPTION

The individual part of the RAE Antenna Capacitance Probe will be discussed in some detail in this section of the report. The progression to be followed is:

- 4.1) Counter, transfer gates and shift register
- 4.2) Purpose of control logic
- 4.3) Functional operation of control gates
- 4.4) Control gates input and output timing signals
 - 4.4.1 Oscillator gating
 - 4.4.2 Transfer pulse
 - 4.4.3 Relay Driver pulse
 - 4.4.4 Reset pulse
 - 4.4.5 Shift pulse
- 4.5) Development of control signals
- 4.6) Relay Driver circuitry
- 4.7) Oscillator circuitry
- 4.8) Limiting and squaring circuitry
- 4.9) Output buffer and send shifter

4.1 COUNTER, TRANSFER GATES AND SHIFT REGISTER

The frequency counting and storage circuitry, comprising the counter parallel transfer gates and circulatory shift register is shown in the overall schematic. The counter is made up of 17 conventional ripple through divide by two-binary frequency divider stages; stage 17 of which registers the most

significent bit. In using 17 binary stages to count 2 megacycle by accurately counting for 100 milliseconds the counter has the capability of counting a decimal number as high as 131,071. Since the counting time is .1 second or 100 milliseconds the conversion factor between the actual frequency of the oscillator and the number in the counter is 10, therefore the highest frequency capability of the counter is 1,310,710 cps. Although the calibaration frequency of the high frequency oscillator is one megacycle or 100,000 as read by the counter, it is not anticipated that the capability of the counter will be exceeded when the antenna is substituted for the calibrating capacitor. If however this should occur, the counter would begin counting over at a frequency of 131,172; hence the maximum frequency would be added to the frequency read out of the counter.

The last 15 stages of the counter are Texas Instrument SN5112 integrated circuit Flip-Flops, which are rated at a maximum of one megacycle. To insure the reliability of this counter, two high speed flip-flop, Signetics SE124G's were used for the first 2 stages, whereby the SN5112 will now see a maximum of 250 kcs. By using different I. C. components for the first two stages of the counter however, required that the logic levels be compatible, hence the inverter between the 2nd and 3rd stages. This compatibility requirement also caused an additional circuitry to be added to the reset line driving only the signetic stages. While all 17 stages of the counter reset from the same reset pulse, the last 15 T. I. stages only require one inverter, however, the first two high frequency Signetic stages require 2 inverters in the reset line for logic compatibility.

The transfer gates are Texas Instrument SN516A operated as Nand Gates. If the side of the counter stage driving a transfer gate is a "one" when the transfer pulse occurs, then this "one" is transferred to the appropriate shift register. The transfer of information from the counter to the shift register is done in parallel with the occurance of the transfer pulse, however serial transfer is performed once the information is in the register with the occurance of shift pulses.

The first 17 stages of the shift register are T. I.'s SN5111, the 51 following are SN510's, the reason for the difference being that the first 17 stages accept the information from the counter, therefore must have the capability of set, reset, and shift pulse, while the 51 following stages only need the capabilities of reset and shift pulse.

The register being a uni-directional circulating type of shift register necessitates that the output of the 68th stage be connected to the first stage which is shown in the overall schematic diagram. Thus shifting one bit at a time, requires 68 shift pulses for all information to be fed to telemetry. This shift rate occurs at a 400 cps rate which would thus require 170 milliseconds for the total transfer of information to be shifted out, and the information to be placed in its initial position within the register.

All stages of the register are essentially of the RS type and the interconnections between stages are indentical. Since a shift register requires temporary storage between two adjacent flip-flops. The state of one flipflop being changed is stored and used as the input to the subsequent flipflop stage. That is the steering diodes or circuitry of the nth stage are
tied to the nth-1 stage and the output of the nth stage drives the nth+1 stages
steering circuitry.

4.2 CONTROL LOGIC

The purpose of the control logic circuitry is to generate timing pulses at the correct time and of the correct length which will:

- (a) control which oscillator is on
- (b) control the mode of the oscillator (antenna or calibrate)
- (c) control the length of time an oscillator is on
- (d) shift the register
- (e) transfer the information in the counter to the register
- (f) reset the counter
- (g) control the counting time of the counter
- (h) prevent the register from over flowing before shift out command
- (i) provide shift out upon shift command

The only input to the control logic circuitry are the 400 cps clock pulse, the read or accumulate command and the shift command. Hence the proper control pulses are generated internally using these three input signals and Texas Instrument and Signetics integated circuits; specifically Flip-Flops, Nand Gates, OR Gates, oneshot multivibrators and "clock" drivers.

4.3 FUNCTIONAL OPERATION OF CONTROL GATES

In the interest simplicity and clarity a step-by-step operational description will be presented, followed by the timing signals generated internally and applied to the control gates and interface circuitry between the gates and counter-memory circuitry. Subsequently the generation of the timing signals will be discussed.

Assume that the information contained in the register has been sent to telemetry and that the power has been shut-off, then at some time t_n , the power is reapplied. A minimum delay of 2.5 seconds (tn+ 2.5 sec.) is required for oscillator stability before the Read Command can be applied; hence the read command occurs at tn + 2.5 + t acting as a reset pulse. The reset or Read command pulse resets the counter, logic circuitry and clears the shift register.

Immediately after the reset, the low frequency oscillator in the calibrate mode is allowed through the NAND gate A HG1/2 (terminal 2 of gate A HG1) and through the OR gate A HG1/2, 9, 10 (terminals 2, 9 and 10 connected together form one output); the low frequency calibrate is prevented from reaching the counter for 20 milliseconds however, by Nand gate A HG2/9, 2.

During this 20 millisecond delay the following things occur: (2) 5 milliseconds after the reset or read command, the transfer pulse is applied to the transfer gates, (b) 10 milliseconds after reset, the counter is reset.

At the completion of the 20 millisecond delay the Nand gate A HG2/92 is opened for exactly 100 milliseconds and the low frequency calibrate signal is allowed to pass to the counter. During this 100 milliseconds interval while the counter accepts and counts the low frequency calibrate signal, there are 17 shift pulses applied to the shift register, at a rate of 200 cps. The shift pulses occur 27.5 milliseconds after the counter begins counting and since it takes 82.5 milliseconds for the 17 pulses to be applied, the shift pulses last until the counter is gated off.

At the same instant the counter is gated off the low frequency calibrate signal is gated off and the high frequency calibrate oscillator signal is allowed to pass through the Nand gate A HG1/10 and the OR gate A HG1/9, 2. 10 but is delayed in passing to the counter again for 20 milliseconds while the transfer pulse and counter reset pulse is applied as previously explained. At the end of the 20 millisecond delay the Nand gate A HG1/92 is again opened for exactly 100 milliseconds and the counter accepts this frequency. Again while this is happening the information now contained in the first 17 stages of the shift register (low frequency calibrate) is shifted to the second 17 stages of the shift register by the 17 shift pulses passing through the Nand Gate C-G3/8, and OR gate C-G3/8, as previously explained.

At the completion of the second 100 millisecond count the high frequency calibrate is prevented from reaching the counter by the Nand gates, and the following things occur: the Nand gate B-G7/8 applies a positive pulse which

energizes the relay driver for the low frequency oscillator; the Low frequency Nand gate A HG1/2 is opened. Thus the frequency as seen from the antenna capacitance is fed to the Nand gate A HG2/92. Again this gate is prevented from opening for the 20 millisecond period while the high frequency calibrate signal, still contained in the counter, is dumped into the first 17 shift register stages with the transfer pulse which occurs 5 milliseconds after the start of the 20 millisecond delay, and the counter is reset again at 10 milliseconds in this 20 millisecond period. Following this 20 millisecond delay the counter accepts the antenna determining low frequency signal while the previous 2 signals are shifted down the register 17 stages.

Upon completion of the 3rd count the signal from the low frequency oscillator is disabled from reaching the counter and the low frequency relay driver is disabled.

However, at the instant the low frequency relay driver is de-energized, the high frequency relay driver is energized by a positive pulse from the output of Nand gate B-G6/8 and the read and shift cycle is completed identically to that of the low frequency cycle above. Thus at the completion of the 4th 100 millisecond count period there is information in the counter and in shift register stage 18 through 68.

If there was nothing to shut off this total read-in cycle the whole procedure would repeat at this point- in fact it starts too. However, during the 5th 20 millisecond delay period, not only is the information in the counter put in the

first 17 stages of the shift register, filling it, and the counter cleared, but at the completion of the 20 millisecond delay, the state of flip flop B-FF14 changes so that the Nand gate B-G7/4 will pulse flip flop C-G2/8 and B-G4/9 is disabled until another read command occurs reseting B-FF11. While the counter will continue to count there will be no further transfer pulses occuring to dump the counter information into the shift register; the only shift pulses which can now occur are generated by the shift command which would apply 68 pulses from the spacecraft 400 cps clock through Nand gate C-G3/4 and OR gate C-G3/8 to shift the information contained in the shift register to telemetry at the same time re-circulating the information within the register.

4.4 CONTROL GATES INPUT AND OUTPUT TIMING SIGNALS

The inputs and outputs to the above gates and the counter memory interface circuitry will be shown consistant with the assumptions made previously. It is important to note at the outset that all T. I. 's Nand gates use logic levels which are complimentary to those of the Signetic Nand gates; failure to do so will result in improper synchronization of the relay drivers.

4.4.1 Oscillator Gating

As shown in Figure 4.1A, the gating signal to the Nand gates controlling output of the oscillator shapes are developed from opposite sides of a flip-flop; hence when one gate is "open" the other is shut. Further gating is provided by another Nand gate controlled by a flip flop whose normal mode

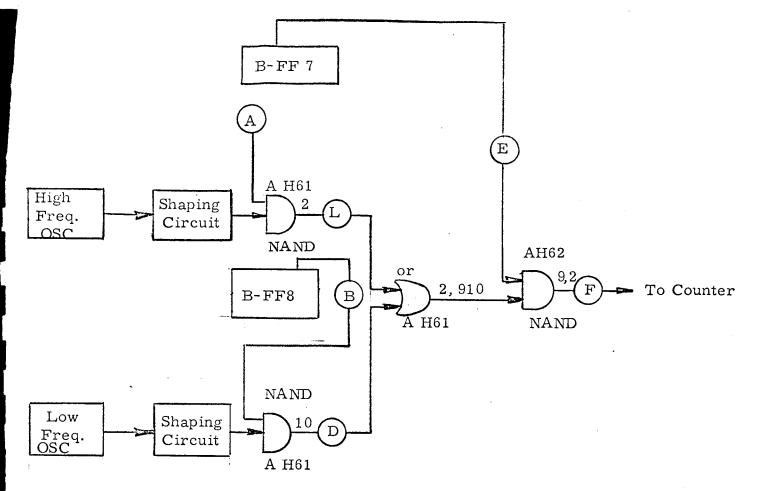


Figure 4.1 A Count Control Circuit

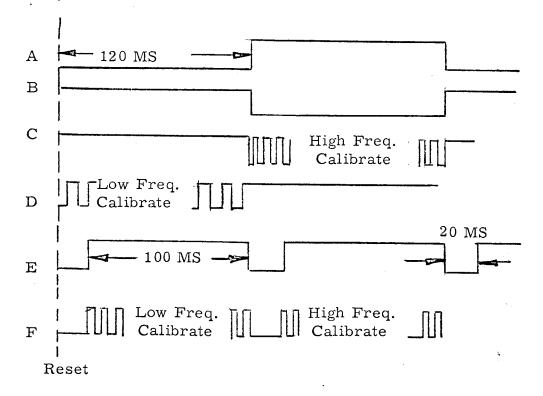


Figure 4.1 B Input & Output to Count Control Circuitry

is disrupted giving the output (signal E) as shown in figure 4.1B. It is this gate and its control which provides the 20 millisecond delay in which the transfer and reset pulses are generated. The output of the last Nand gate goes directly to the counter with no interface circuitry.

4.4.2 Transfer Pulse

of oscillator information to the counter, the transfer pulse is generaged.

The associated circuitry for the generator is shown in figure 4.2A. At this point it should be noted that signal E of figure 4.1B is signal A in this presentation, being developed from C-FF7. The flip flop counter circuitry B-FF12,13 and 14 is being driven from this signal, and in effect count the number of times this signal appears at the input. As long as signals D and F are down (low), Nand gate B-G4/9 will pass the pulse generated by signal E. Signal E is passed through one shot mutivibrator having a pulse duration of approximately 11 usec. Before going to the transfer gate it is passed through an inverter for logic compatibility. Like C-FF7, the flip flop C-FF10 is a binary frequency divider which has had its regular output modified; the method of accomplishing this will be shown later.

4.4.3 Relay Driver Pulse

The method of generating the relay driver pulses are also shown in figure 4.2A. The 3 flip flop binary counter which drives Nand gate B-G4/8 also drives 2 additional Nand gates. The output of these gates go directly to the

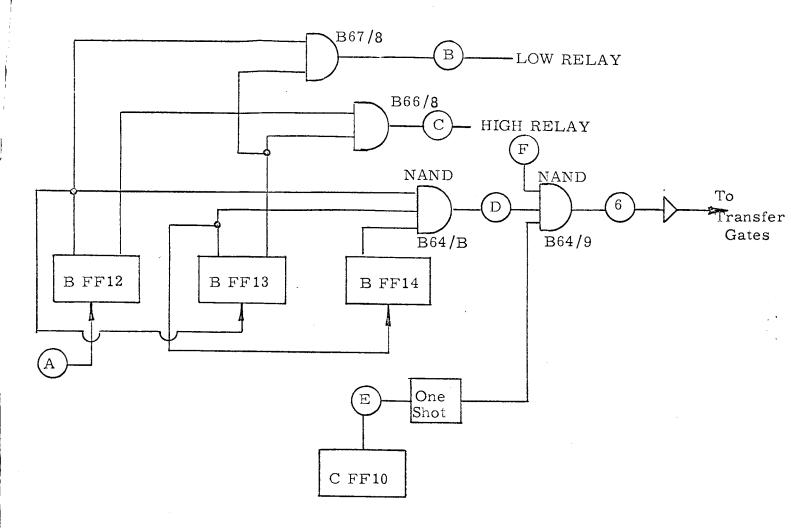


Figure A. Relay Driver and Transfer Pulse Circuitry

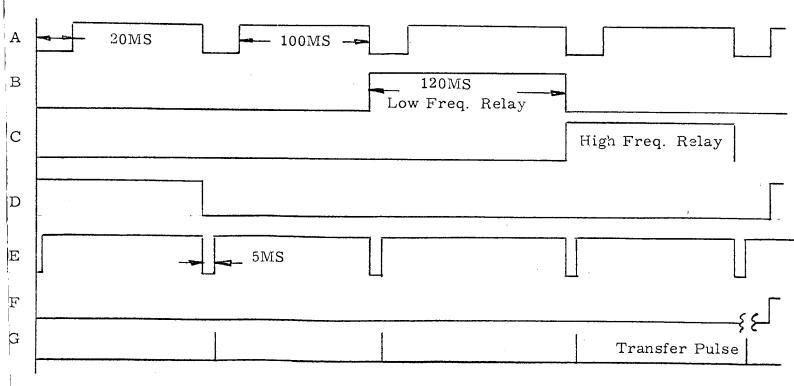


Figure 4.2B. Timing Pulses for Relay Drivers and Transfer Pulses

inputs of the relay driver. Hence when the carry side of BFF12 and BFF13 are high there is an output from Nand-gate B G6/8 which will energize the high frequency relay driver. The output sequency of these gates is shown in figure 4.2B.

4.4.4 Reset Pulse

As mentioned previously the read command is really a reset pulse, reseting the entire instrument. The counter on the other hand can be reset periodically from internal circuitry as shown in figure 4.3A. Because the reset signal to the shift register is a DC level rather than a pulse the R-C integrating interface circuitry shown is to present stray pulses from perhaps accidently reseting a portion or stage of the shift register.

The binary frequency divider flip flop C-FF9 has had its normal mode interrupted similar to CFF7 and CFF10; its output is shown in figure 4.3B. The output of this flip flop, sent through a non-inverting one-shot multivibrator with a pulse duration of approximately 11 usec., forms the counter reset pulse which occurs during the 20 millisecond delay of oscillator information to the counter. Signal C of figure 4.3B is not used in the generation of the counter reset pulse, but is included only to show the occurance of the reset pulse in reference to it.

The dual inverters driving the first two stages of the counter are only for logic compatibility for the high frequency stages as previously explained.

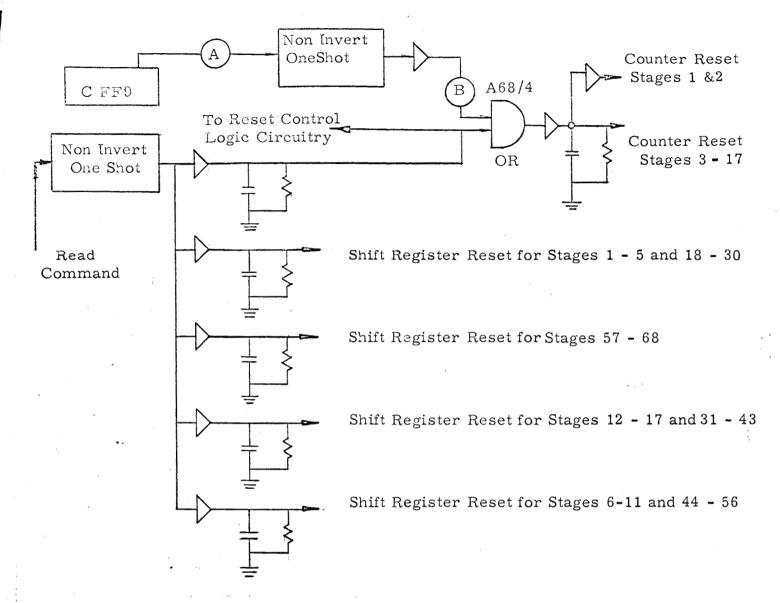


Figure A. Counter and Shift Register Reset Circuitry

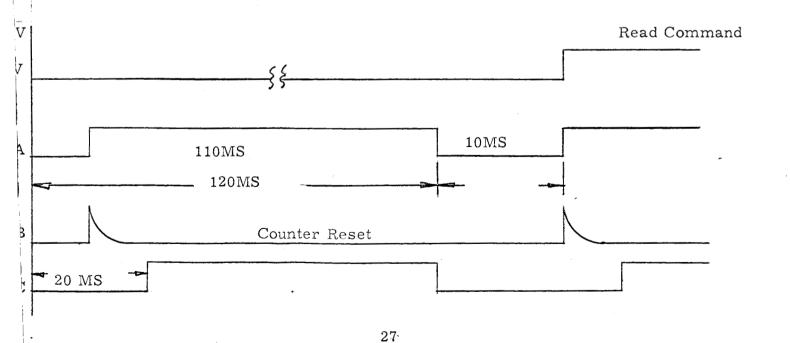


Figure 4.3B. Read Command and Counter Reset Pulses

4.4.5 Shift Pulse Circuitry

The shift pulses to the register occur at two rates; 17 pulses at the rate of 200 per second after each transfer pulse lasting for 82.5 millisecond, and 68 pulses occuring at the rate of 400 pulses per second gated in coincidence with the shift command, lasting for 168.75 millisecond for read out to telemetry. The circuitry and signals generating these pulses are shown in figure 4.4A and B respectively.

The 68 shift pulses occur whenever the shift command opens Nand Gate C-G3/4 allowing the 400 cycle clock to be applied to the shift pulse lines. The 17 shift pulses are generated internally yet derived from the 400 cps clock pulse. As long as signals G and H are such that Nand gate C-G2/8 is open the shift pulses actually are the pulses coming from C-FF1, which is a binary frequency divider being driven from the 400 cps clock pulses; hence the output of this flip flop is at the rate of 200 cps.

The read command will reset B-FF11 such that signal H would open Nand gate C-G2/8, and this signal will not change until 4 sets of 17 shift pulses have been applied to the shift register. Actually B-FF14 will set BFF11 after counting 4 input signals from C-FF7.

This then leaves signal G, which is gated by signals D & E as the largest controlling factor of gate C-G2/8. Signal E is dependent upon the same as signal A. Signal D on the other hand is generated from a divide by three circuit which is "up" once for every 3 times signal C is up. The output

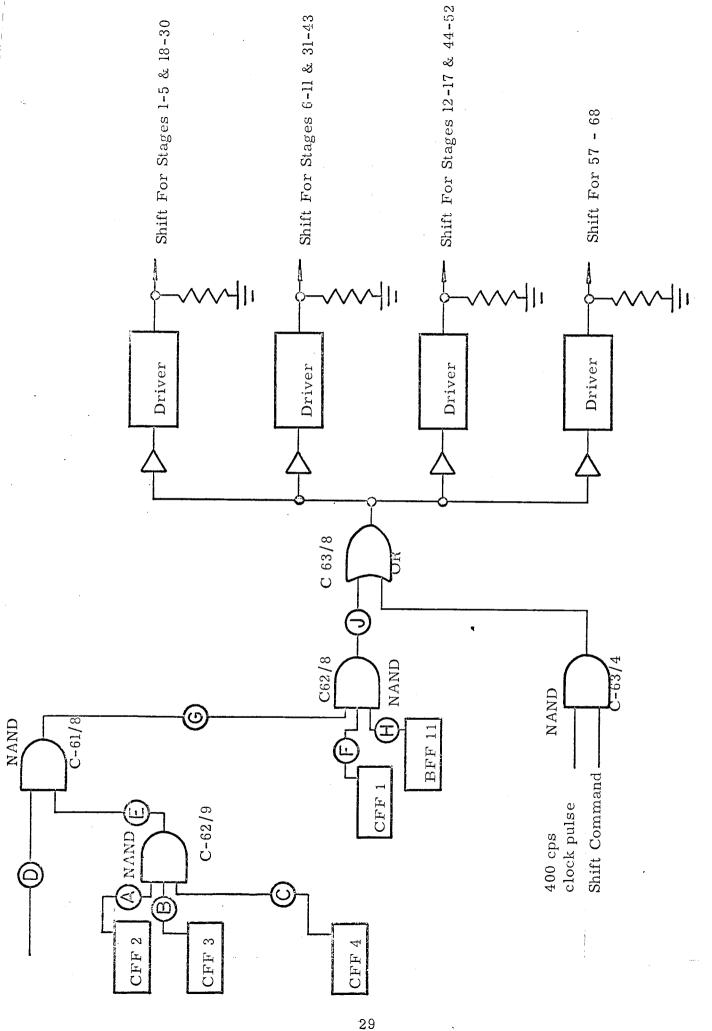


Figure 4.4A Control And Development Of Shift Pulses

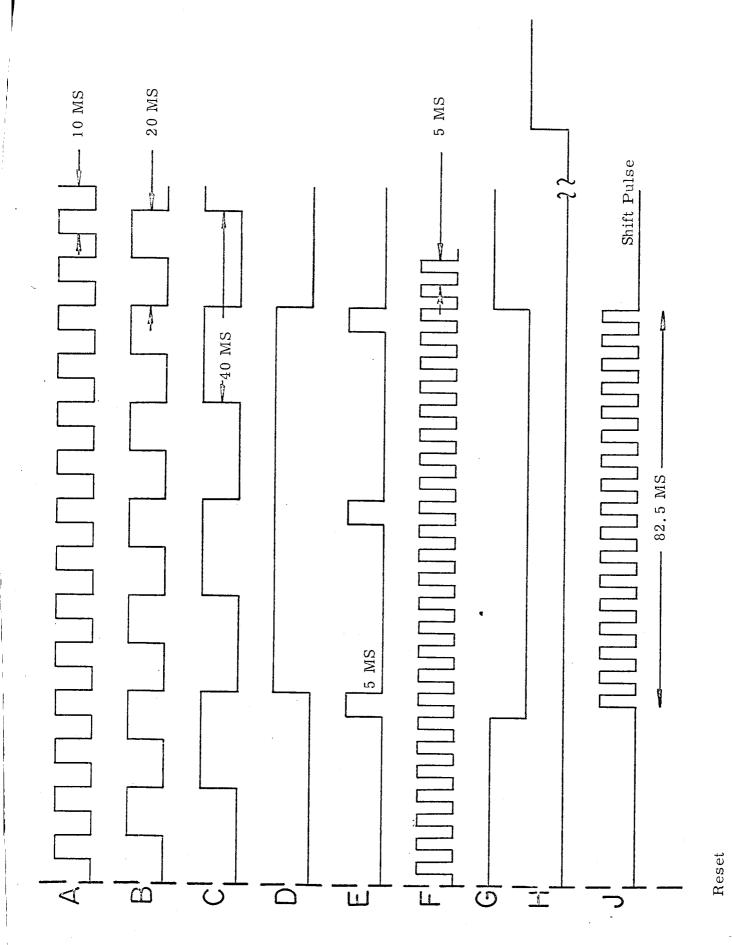


Figure 4.4B Input And Output Signals To Control Shift Pulses

of Nand gate C-G1/8 will be up, thereby shutting off Nand gate C-G2/8, anytime signals D and E are both down. Whenever either or both signals D and E are up however, signal G will be down, and until signal H changes will open Nand gate C-G2/8 to pass the output of C-FF1.

The clock drivers in the shift pulse lines are present to insure sufficient drive capabilities to all 68 stages of the register, since each driver is only capable of driving 20 stages.

4.5 DEVELOPMENT OF CONTROL SIGNALS

The circuitry necessary to develop the proper control signals to be applied to the control gates is shown in figure 4.5 A, while the outputs of each stage is shown in figure 4.5B. All ten flip flops used in this circuitry are basically of the RST type. While each flip flip has the capability of its regular outputs, that is Q and \bar{Q} , they also have additional capability of those outputs from a low impedance emitter follower. In the interest of simplicity however only one side of the outputs have been shown in figure

The first stage is driven by the spacecraft 400 cps clock pulse; signal labled A. All ten stages are reset by the arrival of the read command pulse to the reset input. Each of the first four stages act as a standard ripple through divide by two binary counter stage. The second stage while driving the T input of the third stage also applies its output to the set input of the tenth stage. Similarly the output of the 3rd stage drives the T input of the fourth stage and in addition provides an input to the set input of the ninth stage. The fifth and

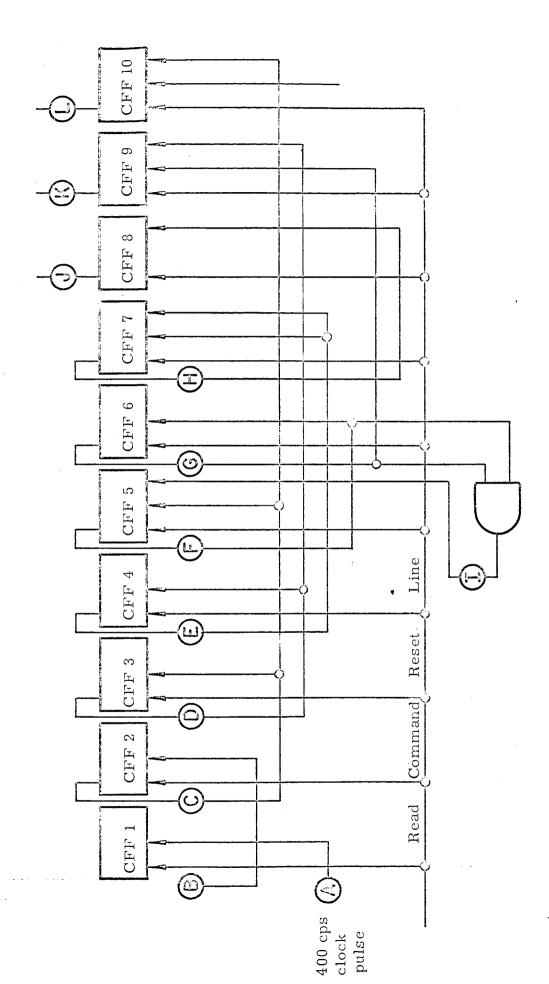
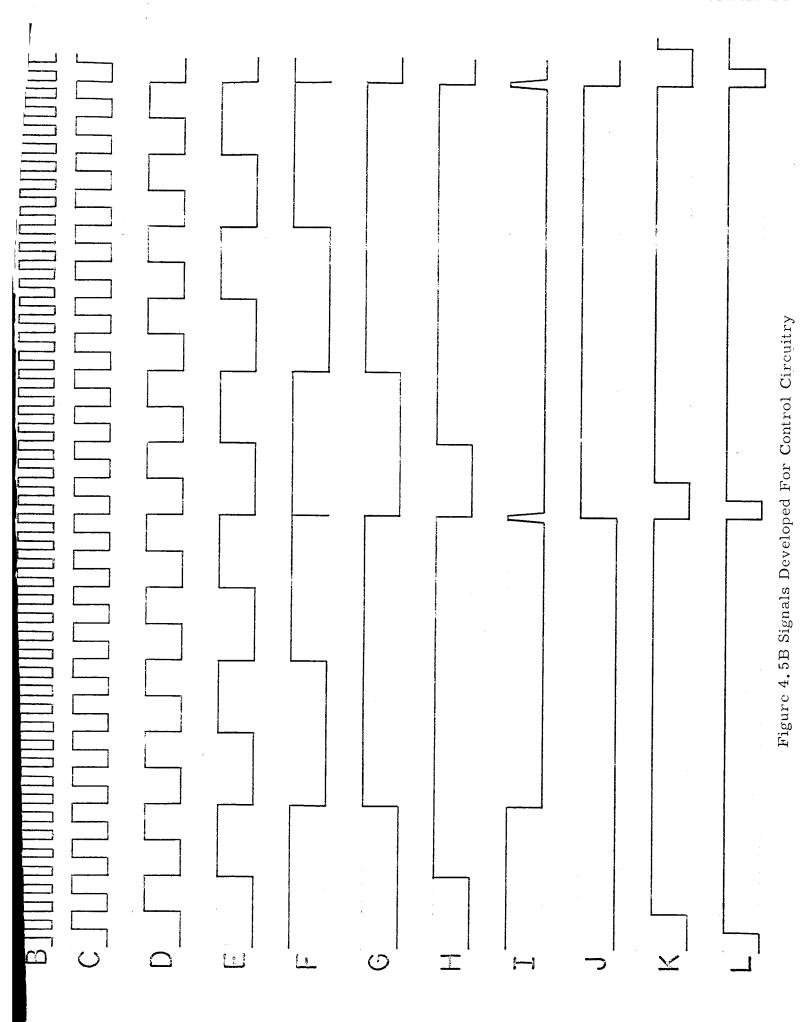


Figure 4, 5A Control Signal Development Circuitry



sixth stages together with the associated Nand gate provide a divide-bythree circuit; the output of the sixth stage driving the T inputs of the seventh, ninth and tenth stages.

4.6 RELAY DRIVER OPERATION

Because the low frequency oscillator relay pulls in first, the relay driver will be described in terms of this driver, however both relay drivers are identical. The circuitry for these drives are shown in the overall schematic.

Before the arrival of the actuating pulse the base of \mathbf{Q}_3 is at ground potential. Thus forward biasing this emitter follower; hence at full saturation approximately one-half volt is developed across it. Because of the low positive voltage at the junction of the 3.9K ohm and 1.5K ohm resistors the base of \mathbf{Q}_4 is biased off at approximately -5 volts, hence the relay is de-energized.

With the arrival of a positive 3.5 volt pulse to the base of \mathbf{Q}_3 the bias on the PNP transistor \mathbf{Q}_3 is now such as to apply reverse bias to the base-to-emitter junction, thereby cutting off this stage. With the emitter follow cut-off the base potential of the NPN \mathbf{Q}_4 becomes positive, putting this transistor into full saturation, and the appropriate relay will be energized thus switching the appropriate oscillator from the calibrate capacitor to the antenna and its capacitance.

The positive pulse (+3.5V) which is sent to the relay drivers will last for 120 millisecond and is developed from the control logic circuitry. As can be seen from Figure 4.2B during the first two 120 millisecond periods the

Capacitance Probe is on and neither relay is energized, then the low frequency is energized for the 3rd 120 millisecond intervals upon completion of which the low frequency relay is again de-energized and the high frequency relay driver is energized for 120 milliseconds during the 4th interval.

4.7 OSCILLATOR CIRCUIT

The oscillator circuit is shown in figure 4.6A, while the AC equivalent circuit for this oscillator is shown in figure 4.6B. Both the high and low frequency oscillator circuits are identical with the exception of some values of resistors, capacitors and the baluns; thus the description will be made in terms of the high frequency circuit. The calibration frequencies are one megocycle for the high frequency and 750 kc for the low frequency oscillator.

Resistors R33, R34, R35 and R36 determine the bias point and hence the quiescent operating point of transistor Q_7 . Similarly for the emitter follower resistors R37, R38, R39 and R40 determine the quiscent point for Q_8 . The oscillator output signal is developed across R36, the emitter AC load resistor and coupled through C18 to the emitter follower buffer stage.

The operation of the oscillator is more simply seen if the parallel capacitors are grouped into one equivalent capacitance as shown in figure 4.6B. The signal developed across R35 is fed back to the junction of C_2 and C_3 sustaining oscillations at the frequency determined by L_1' , C_1' , C_2' , C_3' and the reflected capacitance from the primary of the transformer. Capacitors C_{16} and C_{17} offer

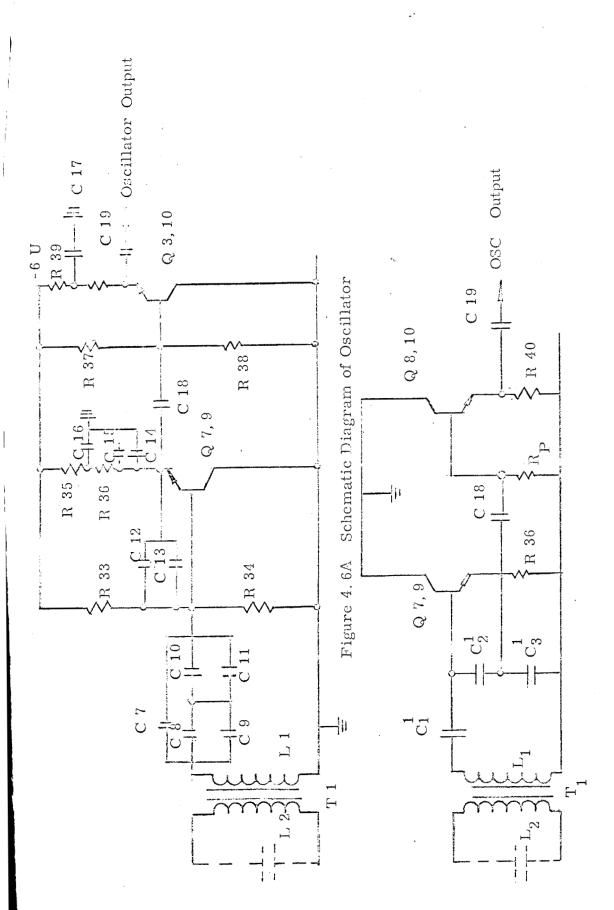


Figure 4.6B. A.C. Equivalent Circuit of Oscillator

a low impedance path for AC thereby effectively grounding R35 and R39 hence the AC load impedance is R36 and R40 for each stage.

4.8 LIMITING AND SQUARING CIRCUIT

The output of each oscillator is fed to separate squaring circuitry, both of which are identical; this circuitry is shown in figure 4.7A. The output of the oscillators are sinusoidal, however, to be fed to the counter the waveform must be squared, or formed into pulses which can be counted by the conventional ripple through binary counter.

The 10K ohm resistor at the input to the schmitt trigger serves as a isolation resistance and also forms part of the gain relationship for the Fairchild F-710C Amplifier. The ratio of the 200K ohm feedback resistor to the 10K ohm input resistance determines the gain of the amplifier, which is 20. The diodes at the input to the Fairchild amplifier will limit the sinewave input to approximately + .6 volts to prevent damage to the amplifier.

Since the input signal to the F-710 amplifier is fed to the inverting input, as the input signal goes positive, the output will go negative and because of the gain, the amplifier will go into saturation, giving a -3 volt output until the input signal again goes through zero whereupon the output is again saturated in the opposite direction to +3 volts. The 10K resistor from the non-inverting input (+) of the Fairchild F-710C amplifier to ground is selected so that both inputs to the amplifier will see the same impedance. The signal has now been transformed from a sinewave to a square wave of the same frequency.

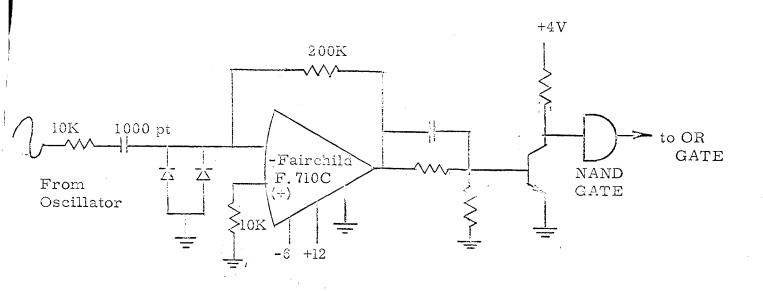


Figure 4.7 Limiting And Squaring Circuit

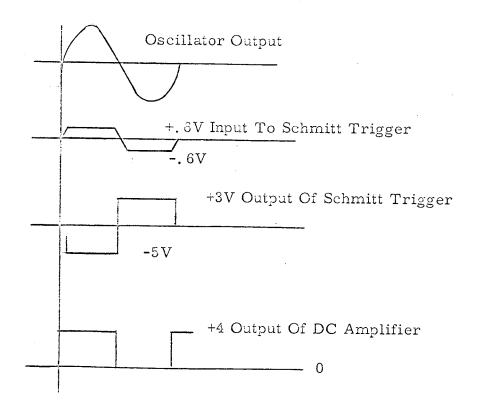


Figure 4.7B Waveforms Of Limiting And Squaring Circuit

The NPN transistor amplifier following the schmitt trigger is used mainly to change the level of the square wave shifting from +4 volts to ground, so that the square wave is compatible to drive the A HG1 Nand gate. When the input to this stage is negative the transistor Q is cut off and the output to the Nand gate is + 4 volts. However, when the input becomes positive the base to emitter becomes forward biased causing the transistor to conduct hard and the output to the Nand gate approaches ground.

4.9 OUTPUT BUFFER AND LEVEL SHIFTER

The output of the 68th stage of the shift register goes to the input of the first stage by trigger steering previously explained, and the output is also to telemetry through a buffer and level shifter stage as seen in the overall schematic.

With the output of the 68th stage at ground potential transistor \mathbf{Q}_{13} is cut-off with approximately -. 64 volts of back bias applied to the base. This means that the base of \mathbf{Q}_{14} is forward biased and this stage is in hard conduction, hence approximately 4. 35 volts would be applied across R 76; thus the output is following the input minus V BE. The diode, CR8, prevents more than .6V reverse bias to be applied to transistor \mathbf{Q}_{14} and also any capacitance discharge loading from the output is fed through the diode and then through the low impedance saturated transistor.

When the positive pulse arrives at the input, Q_{13} becomes forward biased and conduts, placing the junction of R74 and R75 very close to ground

Now \mathbf{Q}_{14} is cut-off and the output zero. Again, should there be any capacitance loading try to discharge through R76 the diode would reduce the impedance with a parallel path. The output voltage levels to telemetry then are ground and 4.3 volts.

V. RELIABILITY AND FAILURE ANALYSIS

5.1 SUMMARY

In accordance with specifications, a reliability analysis of the Antenna Capacitance Probe has been conducted. The specifications require a probability of complete success of at least 0.8 and a probability of complete failure not greater than 0.05. The reliability analysis indicates a probability of complete success of 0.94937 and a probability of complete failure of 0.044012.

5. 2 GUIDELINES FOR ANALYSIS

As suggested by the Military Standardization Handbook "Reliability Stress and Failure Rate Data for Electronic Equipment," MIL-HDBK-217, this analysis assumes that the reliability of complex electronic equipment depends primarily upon the reliability of the parts used in the equipment. The part failure rate is the parameter on which the estimate is made. The part failure rates given in MIL-HDBK-217 are primarily applicable to standard parts subjected to electrical stresses between 0.1 (10%) and 1.0 (100%) of their rated values. Failure data relative to stresses below 0.1 were either statistically insignificant or indicated that 0.1 was the threshold below which little or no reduction in failure rate could be anticipated.

Although a complete reliability analysis should include both catastrophic (random) and performance degradation failures, most degradation failures are eliminated through conservative design. Therefore, equipment failure is

primarily dependent upon the number of catastrophic failures that occur as a function of time.

The following reliability report covers the Radio Astronomy

Experiment and the procedure for this report is based on the following

assumptions: (a) any failure that occurs will be considered a catastrophic

failure; (b) catastrophic part failures occur randomly and exhibit a constant

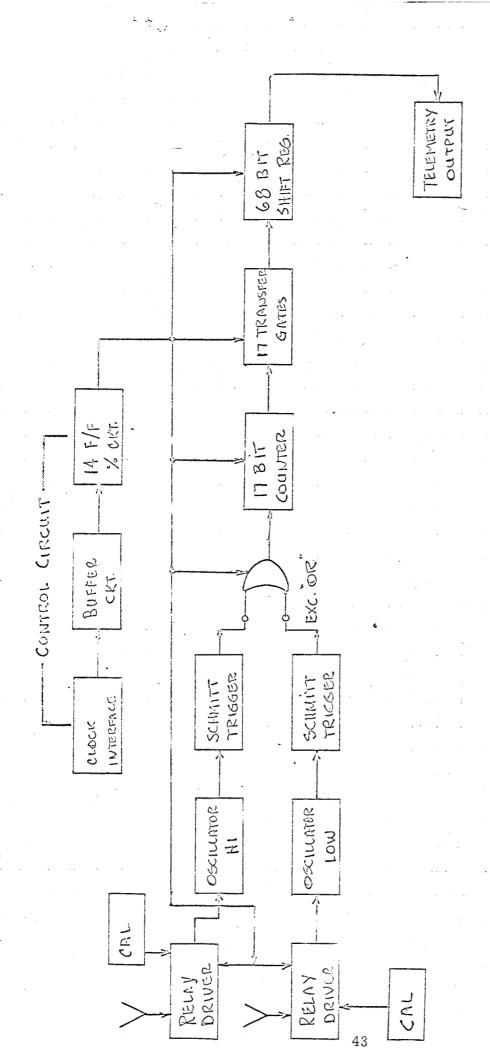
failure rate; (c) all component failures are to be considered catastrophic

failures with certain exceptions.

5.3 SYSTEM RELIABILITY

The system reliability shall be computed on the basis of using most recent, manufactures reliability reports and MIL HDBR 217 to establish those reliability data not available from manufacturers specifications.

The system under consideration is shown in Figure 5. 1. All components are operated at less than 50% of their rated maximum operational specifications. The system can be considered a complete failure if the nexus between input and output is broken due to an open or short failure. The control circuit is not part of the series path for data flow however, its prime function is to give the data to the output and therefore a failure in this function is catastrophic.



SYSTEM BLOCK DIAGRAM

Figure 5, 1

Circuit Tabulation:

"17 Bit Counter"			
Component Type	Manufacturer	Quantity	Total Failure Rate Failure Rate
SN 5112	TI	15	0.016%/1000HR* 0.24%/1000HR
SE 1243	Signetics	2	0.04%/1000HR** 0.08%/1000HR
			0.32%/1000HR
"Transfer Gates"			
Component Type	Manufacturer	Quantity	Total Failure Rate Failure Rate
SN 5161	TI	5	0.016%/1000HR 0.08%/1000HR
SN 516A	TI	. 1	0.016%/1000HR 0.016%/1000HR
			0.096%/1000HR

"Shift Register"

Component Type	Manufacturer	Quantity	Failure Rate	Total Failure Rate
SN 5111	TI	. 17	0.016%/1000HR	0.272%/1000HR
SN 510	TI	51	0.016%/1000HR	0.816%/1000HR
				1 0000//1000

1.088%/1000HR

- ** All Signetics failure data based on interpolated data taken from Signetics memo "Present Reliability Status" 28 February 1964. 60% CL at 55°C
- * All TI Failure report data obtained from 1964 supplement to 1963 Failure Report and is established for 60% CL at 55° C.

"Control Circuit"	•			
Component Type	Manufacturer	Quantity	Failure Rate	Total Failure Rate
SN 511 A	TI	9	0.016%/1000HR	0.144%/1000HR
SN 5111	TI	5 .	0.016%/1000HR	0.080%/1000HR
SN 518A	TI	3	0.016%/1000HR	0.048%/1000HR
SN 517A	TI	. 4	0.016%/1000HR	0.064%/1000HR
SN 514A	TI	2	0.016%/1000HR	0.032%/1000HR
SN 518 A	TI	8	0.016%/1000HR	0.128%/1000HR
Transistor 2N929	TI	2	0.020%/1000HR	0.040%/1000HR
Resistor	Welwyn	15	0.001%/1000HR	0.015%/1000HR
Capicator MC80	Aerovox	9	0.001%/1000HR	0.009%/1000HR
				0.560%/1000HR
"Exclusive Or Gate	· · · · · · · · · · · · · · · · · · ·			Marka I
Component Type	Manufacturer	Quantity	Failure Rate	Total Failture Rate
SE 115G	Signetics	.2	0.04%/1000HR_	0.08%/1000HR
				0.08%/1000HR
"Schmitt Trigger"				
Component Type	Manufacturer	Quantity	Failure Rate	Total Failure Rate
F 710 IC	FCHD	1	0.020%/1000HR	0.020%/1000HR
Transistor 2N929	TI	1	0.020%/1000HR	0.020%/1000HR
Diode 1N916	FCHD	2	0.010%/1000HR	0.020%/1000HR 0.020%/1000HR
	r Chi	4	0.010/8/1000HR	0.02070/1000nR
Capicator MC 80	Aerovox	2	0.001%/1000HR	0.002%/1000HR
Resistor				
F-25 1/4W	Welwyn	6	0.001%/1000HR	0.006%/1000HR
	4	15		.068%/1000HR

"Relay Driver"				5 7
Component Type	Manufacturer	Quantity	Failure Rate	Total <u>Failure Rate</u>
Transistor 2N 871	FCHD	2	0.020%/1000HR	0.040%/1000HR
Diode 1N916	FCHD	,1	0.010%/1000HR	0.010%/1000HR
Relay BRJ12C1P8AS	Filtors	1	0.011%/1000HR	0.011%/1000HR
Resistor F-251/4W	Welwyn	3	0.001%/1000HR	0.003%/1000HR
		•		0.064%/1000HR
"Oscillator"	•			
Component Type	Manufacturer	Quantity	Failure Rate	Total Failure Rate
Transistor 2N 915	Tī ,	2	0.020%/1000HR	0.040%/1000HR
Transformer	WTA	1	0.050%/1000HR	0.050%/1000HR
Capicator DM 15	ARCO	13	0.001%/1000HR	0.013%/1000HR
Resistor F-251/4W	Welwyn	8	0.001%/1000HR	0.008%/1000HR
				0.111%/1000HR
"Calibrate Network"	_	••		
Component Type	Manufacturer	Quantity	Failure Rate	Total Failure Rate
Capicator DM 15	ARCO	2	0.001%/1000HR	0.002%/1000HR
				0.002%/1000HR
"Telemetry Output"				m ; 1
Component Type	Manufacturer	Quantity	Failure Rate	Total Failure Rate
Transistor 2N930	TI	2	0.020%/1000HR	0.040%/1000HR
Diode 1N916	FCHD	1	0.010%/1000HR	0.010%/1000HR
Capicator DM 15	ARCO	1	0.001%/1000HR	0.001%/1000HR
Resistor F-25 1/4W	Welwyn	6	0.001%/1000HR	0.006%/1000HR
				.057%/1000HR

Miscellanecus	M	isc	ella	nec	is
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Component Type	Manufacturer	Quantity	Failure Rate	Total Failure Rate
Filter Capicator (Tantalum)	Sprague	8 .	0.012%/1000HR	0.096%/1000HR
Connectors	Cannon	2-1a 1a		0.011%/1000HR 0.004%/1000HR
	i=N	•		0.021%/1000HR

λ; = Part Failure Rate (%/1000HR)

17 = Composite Failure Rate for the Part Group Under Study

Item		Total Failure Rate (%/1000HR)
17 Bit Counter		0.32
Transfer Gates		0.096
Shift Register		1.008
Control Circuit		0.560
Exclusive Or Gate		0.080
Schmitt Trigger	2 a 0.068	.136
Relay Driver	2 a 0.064	0.128
Oscillator	2 a 0.111	6.222
Calibrate Network	2 a 0.002	0.004
Telemetry Network		0.057
		2.611 %/1000HRS

 γ = 2.611 - The total is in accordance with a 60% confidence level and TA= +55 $^{\circ}$ C (Max thermal stress)

The probability of complete success of the entire Experiment Package:

where t = total operating time

t = 2000 HRS

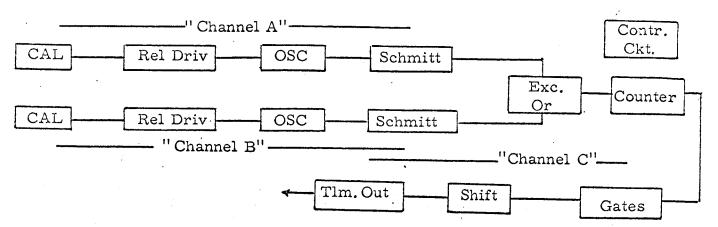
.. Ps = @ -(2.611%/1000HRS)(2000 HRS)

Ps = 0.94937

Mean Time Between Failure MTBF = $\frac{1}{\lambda_T}$ = 38.250 x 10³ HRS

P s including 400 hrs. test time = 0.93950

Probability of Total Failure



Pa = Probability of success of Channel A

Pb = Probability of success of Channel B

Pc = Probability of success of Channel C

Failure Rate of Channel "A"

Cal. Network

.002%/1000HR

Oscillator

.111%/1000HR

Relay Driver

.064%/1000HR

Schmitt Trigger

.068%/1000HR

.245%/1000HR

-. 245%/KHR(2000HR)

Pa = C

Pa = 0.99512

Failure Rate of Channel "B"

Pb = Pa = 0.99512

Failure Rate of Channel "C"

1.121%/1000HR

$$Pc = \frac{1}{1.046} = 0.95602$$

 \mathbf{B}

В

Pc Fail = 1 - Pc = .04398

Probability Table

 $_{\mathrm{B}}$

 \mathbb{B}

_	•			= Criteria for total	failure
Channel A	Channel B	Channel C		B = Bad	
			•	G = Good	,
В	G	G		•	
G	G	G			,

G ✓

Pf = Pc
$$(1-Pa)^2 + (Pa-Pa^2) (1-Pc) + Pa^2 (1-Pc) + (1-Pa)^2 (1-Pc)$$

+ $(Pa-Pa^2) (1-Pc)$

=
$$Pc (1-Pa)^2 + 2 (1-Pc) (Pa-Pa^2) + Pa^2 (1-Pc) + (1-Pa)^2 (1-Pc)$$

= 23.698
$$\times$$
 10⁻⁶ + 433.364 \times 10⁻⁶ + .04355 + 1.0473 \times 10⁻⁶

Pf = 0.044012

APPENDIX A SPECIFICATION FOR ENGINEERING MODEL OF THE CAPACITANCE PROBE

1. SCOPE

The unit supplied will be used in engineering integration tests of the electronic system of the RAE satellite. The purpose of these integration tests in to make possible the writing of an accurate specification for the prototype and flight models of this unit for the satellite. This satellite will be a non-scaled satellite with a circular orbit inclined 50 degrees to the equator at an altitude of 6000 kilometers.

2. APPLICABLE DOCUMENTS

The provisions of the following specifications, standards, drawings and publications of date of current issue will apply as detailed in this specification.

In the event of a conflict, the detailed provisions of this specification shall govern.

MSFC Std. 154	Printed circuit design and construction.
MS 33586	Metals, definition of dissimilar electric.
MIL-I-6181D	Interface control requirements, air-
	craft equipment.
S-320-D1	General environmental test specification
	for Spacecraft and components.
GSFC TID-S-100	Specification for contractor-prepared
	monthly, periodic, and final project
	reports.
GSFC X623-63-147	Specification drawings, engineering and

associated lists.

MIL-JDBK-217		Reliability stress and failure rate data
		for electronic equipment.
GSFC-P	PL-3	Preferred parts list.
FED-ST	D-102	Preservation packaging, and packing
		levels.
FED-ST	D-123	Marking for domestic shipment.
2.1	Mechanical Drawings	
	GB-RAE-1155-001	Standoff
	GB-RAE-1155-002	Insulator Board
	GB-RAE-1155-003	Spacer
	GB-RAE-1155-004	Can
	GB-RAE-1155-005	Encapsulation Procedure
	GC-RAE-1155-009	Retaining Strip
	GC-RAE-1155-011	Rear Panel
	GD-RAE-1155-500	Container Cover
	GD-RAE-1155-505	Cover
	GD-RAE-1155-504	Right Side Panel
	GD-RAE-1155-507	Container
	GD-RAE-1155-511	Left Side Panel
	GF-RAE-1155-512	Capacitance Probe Electronic Enclosure
		Assembly

GF-RAE-1155-513 Front Panel

2.2	Electrical Drawings	
	GC-RAE-1155-006	Printed Wiring Assy Control #4
	GC-RAE-1154-007	Printed Wiring Board Control #4
	GC-RAE-1155-008	Printed Wiring Main Board
	GC-RAE-1155-010	Printed Wiring Board Test Limiter
	GR-RAE-1155-101	Printed Wiring Assy Shift Register
	GD-RAE-1155-203	Welded Module T & R Driver
\$	GD-RAE-1155-204	Printed Wiring Assy Test Limiter
	GD-RAE-1155-205	Printed Wiring Assy RAE Oscillator
•	GR-RAE-1155-206	Schematic Diagram RAE Capacitance
		Probe Experiment
	GD-RAE-1155-402	Printed Wiring Assy Counter Shift
		Register
	GD-RAE-1155-403	Printed Wiring Assy Control #1
	GD-RAE-1155-404	Printed Wiring Assy H. S. Counter
		Shift Register
	GD-RAE-1155-405	Printed Wiring Assy Control #2
	GD-RAE-1155-406	Printed Wiring Assy Control #3
	GD-RAE-1155-501	Printed Wiring Board Control # 3
	GD-RAE-1155-502	Printed Wiring Board H. S. Counter Shift
		Register
	GD-RAE-1155-503	Printed Wiring Board Shift Register

	GD-RAE-1155-506	Printed Wiring Board Control #2
	GD-RAE-1155-508	Printed Wiring Board Control Circuit#1
	GD-RAE-1155-509	Printed Wiring Board Counter Shift
		Register
	GD-RAE-1155-510	Printed Wiring Board RAE Oscillator
	GR-RAE-1155-514	Printed Wiring Assy Main Wiring
2.3	Other Documents	
	Report No. NAS 9175-1	Final Report on "Engineering Model of
		Antenna Capacitance Probe", Part No.
		2158-R-434, under Contract No.
		NAS 5-9175

3.1 REQUIREMENTS

The capacitance probe shall be designed and constructed to satisfy all of the requirements specified herein.

3.1 General

3.1.1 Materials

Materials and processes uded during manufacture of items covered herein shall be of high quality, suitable for the purpose, and conform to applicable government and contractor's specifications whenever possible. Materials and components of proven reliability shall be employed to the greatest practicable extent.

3.1.1.1 Metals

All metals which are used in the construction of the items covered by this specification that are subject to deterioration when exposed to the climate and environmental conditions specified in U. S. Government Spec. S-320-D1 shall be protected in a manner that will in no way prevent compliance with this specification. The use of protective coatings that will crack, chip or scale with age or extremes of climatic and environmental conditions shall be avoided.

Dissimilar metals as defined by MS 33586 shall not be used in intimate contact unless protected against electrolytic corrosion.

3.1.2 Interchangeability

All parts having the same manufacturers parts numbers shall be directly and completely interchangeable with each other with respect to installation and performance, except as approved specifically by the purchaser.

3.1.3 Workmanship

"The units including all parts and accessories shall be manufactured in a thorough workmanlike manner in accordance with best commercial practice. The provisions of MSFC 154, 270, 271 and NPC 200-4 shall be applicable. Component interconnections shall be soldered."

3.2 Electrical Requirements

The capacitance probe shall monitor a dipole antenna in accordance with the operational program of spacecraft and shall develop a signal which indicates the capacitive reactance of the antenna. This isgnal shall be processed and stored in a format which is compatible with the spacecraft telemetry system.

The instrumentation for the antenna capacitance measuring system shall be divided into two packages. One package shall be located near the antennas to be measured and shall contain the capacitance oscillators, the calibration capacitors, and associated switching relays and gates. The main package shall be located in the main body electronics stack and will contain power conversion, counter circuit, transfer gates, shift register, clock frequency conversion logic and control logic.

3.2.1 Antenna Capacitance Oscillator

Two closely coupled oscillators shall be located in the package near the antenna terminstions. These oscillators will operate at 750 kc and 1 mc, respectively. The oscillator design shall be basically LC units with a short term

stability of \pm 0.05% from 2.5 seconds after the application of power until the removal of power. The basic oscillator when connected to the antenna will cause a maximum excitation of 5 volts peak to peak to be applied to the antenna.

The respective oscillators shall assume a calibration frequency of 750 kc and 1 mc when their capacitance standard is switched into the circuit. If the antenna capacitance changes, then the basic oscillator frequency will shift. Therefore, f becomes proportional to c. A DC bias can be applied to the antenna if a desired potential is required between the antenna and the spacecraft.

The oscillators shall assume a calibration frequency of 500 kc when a capacitance standard is switched into the circuit. These calibration circuits shall allow a check to be made on the basic oscillator frequency to determine if a drift is occuring.

Upon command from satellite control circuitry, the oscillators shall be gated with logic gating so that their signals shall pass alternately to the counter circuitry.

3.2.2 Counter

A seventeen stage counter shall be used to count the 4 respective oscillator frequencies, two measuring frequencies and two calibrate frequencies. These seventeen stages shall allow a maximum frequency of one megacycle to be recorded. The counter circuit shall have a sample period of 100 milliseconds.

The basic accuracy of the capacitance measuring system shall be achieved by having a sample period of sufficient time to record the frequency to the desired accuracy and by holding the sampling period very accurately.

3.2.3 Transfer Gates

The transfer gates shall be activated by a control signal at the end of the 100 millisecond sample period. These gates shall transfer the binary information from the counter to the shift register.

3.2.4 Shift Register

The shift register shall be composed of 68 stages which shall allow the storage of four, seventeen bit binary words. After the transfer of each seventeen bits and be ready to accept the next binary word into the register.

The shift time shall be less than 100 milliseconds. The four digital words shall be accumulated and stored in the following order: high frequency calibration; low frequency calibration; high frequency; and low frequency.

Upon command from spacecraft control circuitry, the shift register will accept the spacecraft shift pulses so that the data can be transferred serially. The output of the last shift register stage will be monitored by telemetry. The rate of shift out will be 400 bits per second. The output of the last stage will be buffered to conform to interface requiements as specified by GSFC.

The shift register shall be capable of being cycled at speeds up to 250,000 bits/second.

3.2.5 Experiment Clock

The experiment clock shall operate from the basic satellite clock pulse of 400 cps square wave, and the basic sampling time of the instrument shall be derived from this clock, which has a frequency stability of \pm 0.1 percent.

The experiment clock shall provide reset signals for the counter and the shift register. The clock shall provide transfer signals for the transfer gates, commands for the gates which control the counter input, signals to drive the oscillator calibrate relay, and experiment shift pulses to shift each word in the register during the data accumulation cycle.

3.2.6 Control Signals

The unit shall operate in conjunction with the external control signals listed below.

3.2.6.1 Power Control

Power shall be externally switched on and off to the unit so that power shall be available only during operating periods.

3.2.6.2 Accumulate Command

An accumulate command shall be provided to the unit to start the data accumulation cycle. It shall be provided at not less than 2.5 seconds after power is provided to the unit.

3.2.6.3 Clock Pulses

Clock pulses shall be provided to the unit as discussed in paragraph 3.2.5.

3.2.7 Accuracy

The overall accuracy of the instrument shall be \pm 0.15 percent or better, including the basic satellite clock error.

3.2.8 Power

The unit shall operate from +6 vdc, -6 vdc, and +3 vdc. These voltages are regulated to + 1% maximum power consumption shall not exceed the values given below.

+6 volts 40 MA 0.24 watt
-6 volts 20 MA 0.12 watt
+3 volts 300 MA 0.90 watt

Total Power Dissipation

1.36 watt

Not more than 1.36 watts shall be dissipated by the unit for a period of 3.6 seconds every 10 minutes.

3.2.9 Equipment Grounds

Power supply and signal returns shall be isolated from each other and from the case.

3.1.10 Telemetry

The unit shall be suitable for operation with a PCM telemetry system at a rate of 400 to 800 bits per second.

3.3 Mechanical Requirements

3.3.1 Configuration

The instrument shall be packaged in two sections. The main body shall be a standard RAE instrument can 5×7 inches with a height of 1-1/4 inches. The other package to be located at the antenna base shall not exceed 9 cubic inches. The actual shape shall be specified by GSFC.

3.3.2 Weight

The total weight of this unit shall not exceed 1.75 pounds. Reduction in weight shall be a prime design consideration.

3.3.3 Packaging

The unit shall be packaged modularly using either printed circuit board or welded module techniques. Two contacts shall be provided on the power supply connector (s) for each power supply connection. All exterior surfaces shall be protected from the environment specified.

3.3.4 Marking

The marking must not deface or damage the equipment or affect its functional use. The marking should be legible with the item mounted in normal position. Each item shall be legibly marked with the following information as a minimum.

Specification Number including latest Revision Number

Part Number and Name

Serial Number

Date of Manufacture (month and year)

Contractor's name and trademark

This information shall preferably be applied to a nameplate (or tag on items too small for a nameplate) securely fastened to the item. It may be applied directly to the surface of the item by acid or electric etching, engraving, silk screen process branding, embossing, casting, molding or by the metal-cal process. The permanency of the marking shall be sufficient to withstand the environmental conditions specified. Decals and stencils are not acceptable.

3.4 Environmental Requirements

The unit shall meet all electrical and mechanical specifications throughout the range of environmental conditions specified in this section.

3.4.1 Altitude

The unit shall be capable of operation at a pressure of 10⁻¹³ torr.

Hermetic sealing of parts and assemblies shall be provided to the extent required.

3.4.2 Temperature

The operating temperature range shall be -20° C to $+70^{\circ}$ C, and the highest rate of temperature cycling from one extreme to the other shall be 15 minutes. The storage temperature range shall be -30° C to $+70^{\circ}$ C.

3.4.3 Humidity

The unit shall operate relative humidity range of 0 to 98 percent.

3.4.4 Vibration

The unit shall meet the sinusoidal and random vibration levels as specified in paragraph 4.2.2.

3.4.5 Acceleration

The unit shall meet the acceleration levels as specified in paragraph 4.3.5 of specification S-320-D-1.

3.4.6 Thermal-Vacuum

The equipment shall operate within specification while exposed to 10^{-13} torr over the range of -20° C to $+70^{\circ}$ C.

3.4.7 Radio Frequency Interference

The unit shall conform to the following:

3.4.7.1 Generation

a) Radio Frequency Conducted

The equipment shall be designed to meet the requirements specified in MIL-I-6181D para. 4.3.1 in the frequency range 0.15 to 25 Mc.

b) Low Frequency Conducted

Interface voltages and currents in the frequency range 35 cps to 150 kc in excess of 30 mv and 10 ma peak-to-peak shall not appear on any conductor external to the equipment, which could conduct interference to other equipment.

c) Radiated

Equipment is to meet the requirements specified in MIL-I-6181D para. 4.3.2 in the frequency range 0.15 to 200 Mc.

3.4.7.2 Susceptibility

a) Radio Frequency Conducted

Equipment is to meet the requirements specified in para.

4.3.4.1.1 of MIL-I-6181D. Tests shall be made over 0.15 to 400Mc.

b) Audio Frequency Conducted

No change in indication, malfunction or degradation of performance shall be produced in any equipment when a sine wave signal of 100 mv rms or when a step function or low frequency square wave of 300 mv amplitude having a rise time of less than 1 microsec is applied as shown in Fig. 19 of MIL-I-6181D. Tests shall be made over the frequency range 35 cps to 150 kc.

in performance) during a mission of 10,000 hours (2,000 hours operating time) greater than 0.8 (confidence level 60 percent).

Both of these figures refer to operation in the space environment.

4. SAMPLING, INSPECTION, AND TEST PROCEDURES

4.1 Quality Assurance

The contractor shall conform to specification NASA Quality Publication NPC 200-3, April 1962 entitled, "Inspection System Provisions for Suppliers of Space Materials, Parts Components and Services". Wherever possible, parts shall be selected from the following documents:

- 1) GSFC-PPL-3, 1 Jan. 65, Preferred Parts List,
- 2) JPL Preferred Parts List for Spacecraft Scientific Experiments,
- 3) OGO Electronic Parts Specification Development Guide.

All part ratings shall be derated for design use as necessary to achieve, in conjunction with simplified design and redundance where necessary, the specified reliability for the unit.

The reliability analysis required as a part of the final report shall be based on MIL-HDBK-217, 8 Aug. 62, "Reliability Stress and Failure Rate Data for Electronic Equipment".

All work on this order is subject to inspection and test by NASA or its designated representative at all times (including period of performance) and places.

Final acceptance will be performed at GSFC.

4.2 Test Program

The contractor shall fully test each unit to insure full compliance with all electrical and mechanical requirements of the specification.

Although each unit shall be bench-tested as above, only one unit shall be tested for compliance with the environmental requirements, and only the following tests shall be performed (in the order listed):

- 1) temperature,
- 2) radio frequency interference,
- 3) vibration
- 4) thermal-vacuum

The above tests shall be performed prior to delivery of the units to GSFC.

All measurements shall be made with instruments which have had their accuracy verified periodically against standards traceable to the National Bureau of Standards.

Data shall be provided to GSFC as specified in para. 4.3 of this specification.

4.2.1 Temperature

4.2.1.1 Cold Storage

- a) Thermocouples to indicate temperature stabilization shall be attached to the component in sufficient number and at such locations as to measure the highest and lowest component temperature.

 Stabilization shall be considered achieved when no thermocouple varies by more than 0.5°C/hr.
- b) The instrumented component, while non-operative, shall be placed in a test chamber which shall be stabilized at -30° C $\pm 2^{\circ}$ C. The

- component shall ramain so exposed for six hours.
- Following this exposure, the temperature of the test chamber shall be increased to $+25^{\circ}\text{C} \pm 5^{\circ}\text{C}$ and the component operated typical of orbital flight for sufficient duration to determine compliance with its performance specification.

4.2.1.2 Hot Storage

- a) The component shall be placed in a nonoperative state and the temperature of the test chamber increased in one hour or less to $+70C \pm 2^{\circ}C$. After stabilization of chamber temperature, the component shall remain exposed to $+70^{\circ}C$ for six hours.
- b) Following this exposure the temperature of the test chamber shall be reduced to $+25^{\circ}$ C \pm 5° C and the component operated typical of orbital flight. The duration of operation shall be sufficient to determine compliance of the component with its performance.

4.2.1.3 Operational Temperature

a) The instrumented component, while non-operative, shall be placed in a test chamber. The temperature of the chamber shall be adjusted such that the temperature of the component becomes stabilized at -20°C + 2°C. After temperature stabilization, the component shall be operated for one hour minimum and its performance checked. For cyclically operated components ("on-off" orbital operation), cold start capability shall be demonstrated at least three times. Each cycle of operation shall be

preceded by reverting to stabilized conditions at -20° C $\pm 2^{\circ}$ C. The total duration of operation shall be one hour minimum.

- b) Immediately following the cold temperature exposure, the component shall be turned off and the temperature of the test chamber increased to $+70^{\circ}\text{C} \pm 2^{\circ}\text{C}$. After temperature stabilization, the component shall be operated.
- c) Following this exposure, the temperature of the test chamber shall be reduced to $+25^{\circ}\text{C} \pm 5^{\circ}\text{C}$ and the component operated for sufficient duration to determine compliance with its performance specification.

4.2.2 Vibration

For this test, with the exception of test levels and recording on magnetic tape (recording accelerometer signals shall be recorded continuously; however, the use of magnetic tape is not mandatory) all the requirements of paragraphs 4.1.8 through 4.1.8.5 of specification S-320-D-1 shall apply. Since the tests must be performed in the asbsence of both a representative spacecraft structure and transmissibility measurements, the component shall be attached to the vibration excitor via a rigid fixture. Sinusoidal virbration test levels shall be as specified in paragraph 4.2.2.1. Random virbration test levels shall be as specified in paragraph 4.2.2.2.

4.2.2.1 Sinusoidal Vibration

This test shall be conducted by sweeping the applied frequency once through each range specified in the schedule. The rate of change of frequency shall be 2 octaves per minute.

SINUSOIDAL VIBRATION SCHEDULE

Axis	Frequency Range cps	Test Duration Min.	Acceleration g, 0-to-peak
Thrust	10-50	1.17	3.8*
(Z - Z)	50-110	. 57	1.524 mm(.06 inch)** double amplitude con- stant displacement
	110-200	. 43	37.0**
	200-500	. 66	7.3
	500-2000	1.00	21.0
	2000-3000	1.00	15.0
	Tota	al 4.83 Min.	

SINUSOIDAL VIBRATION SCHEDULE (con't)

Axis	Frequency Range cos		Test Duration Min.	Acceleration g, 0-to-peak
Lateral				
(X-X) and	50-96		1.17 .44	3.0* .584 mm (.023 inch)** double amplitude con-
Lateral (Y - Y)				stant displacement
	96-250		. 72	11.0*
	250 - 500	•	. 50	2.3
	500-2000		1.00	3.8
	2000-3000		1.00	15.0
		Total	4.83 min.	
		(eac	h axis)	

Grand Total: 13.49 Minc.

4.2.2.2 Random Motion Vibration

Gaussian random vibration shall be applied with the "g-peaks" clipped at three times the root-mean-square acceleration specified in the schedule. With the component installed, the control accelerometer response shall be equalized such that the specified power spectral density (PSD) values are within ±3 db throughout the frequency band as determined by the analysis specified in 4.1.8.3 of specification S-320-D-1. The filter roll-off characteristic above 200 cps shall be at a rate of 40 db/octave or greater.

^{*} When the specified accelerations cannot be attained due to armature displacement limitations, the input may be a constant displacement not less than 0.5 in. double amplitude.

^{**} In these frequency ranges, the test levels include the effects of transmissibilities through the spacecraft structure as explained in paragraph 4.3.4 of S-320-D-1.

RANDOM VIBRATION SCHEDULE

Axis	Frequency Range cps	Test Duration Min.	PSD Level g ² /cps	Acceleration g-rms
Thrust (Z-Z) Lateral (X-X) Lateral (Y-Y)	20-2000	4 (each axis)	0.07	11.8
		Total: 12 Min	n.	

4.2.3 Thermal-Vacuum

The component shall be mounted in such a manner that it is thermally isolated from its mounting fixture. The mounting fixture for this purpose shall be designed to minimize interference of radiation paths from the radiant sources to the component. The component shall be installed in the chamber in such a way that it will not be exposed to any abnormally hot or cold source. Thermocouples shall be attached to the component in sufficient number and at such locations as to measure the highest and lowest component temperature. The instrumented component shall be placed in the test chamber, and an operational check shall be performed prior to chamber evacuation. With the component operative, typical of boost phase, the chamber shall be evacuated to 10⁻¹² TORR. Corona effects shall be monitored throughout the evacuation period.

4.2.3.1 Low-Temperature Soak

Immediately following the corona check, the component shall be turned

off and the chamber adjusted such that stable conditions are established at 10^{-13} torr and $-20^{\circ}\text{C} \pm 2^{\circ}$ C. Stabilization shall be assumed when indication from each thermocouple attached to the component does not change by more than 0.5°C per hour. The chamber control shall be held fixed, and the component operated throughou the exposure period of 24 hours. For cyclically-operated components ("on-off" orbital operation), cole start capability shall be demonstrated at least three times during the 24-hour exposure. Each cycle of operation shall be preceded by reverting to stabilized conditions at $-20^{\circ}\text{C} \pm 2^{\circ}\text{C}$. The temperature of the component shall be monitored continuously during the exposure. Performance of the component shall be monitored at least at the beginning and end of the exposure period. For cyclically-operated components, the performance of the component shall be checked periodically, consistent with the test duty cycle.

4.2.3.2 High-Temperature Soak

At the conclusion of the low-temperature vacuum exposure, the chamber conditions shall be altered such that stable conditions are re-established at 10⁻¹³ torr and +70°C +2°C. Stabilization shall be assumed when indication from each thermocouple does not change by more than 0.5°C per hour. When stable conditions have been achieved, the chamer temperature controls and its temperature held fixed. The component shall be operated and its temperature monitored throughout the exposure period of 24 hours. The performance of the component shall be checked periodically as well as at the beginning and end of the exposure period.

4.2.4 Radio Frequency Interference

Test shall be performed to prove complicane with all requirements of paragraph 3.4.7.

4.3 Documentation

The basic philosoply of the data required hereunder is that it must be sufficient to summarize the program, document technical advances, fully describe developed equipment, and in particular, to permit fabrication, adjustment, test and operation of developed equipment by any qualified source.

4.3.1 Monthly Letter Reports

Informal monthly letter reports shall be provided in 3 copies by the 10th of the month following the report (calander) month. They shall comply with requirements of TID-S-100 for type I reports, and shall include:

- (1) summary of work performed during the month;
- (2) special problems and their solutions;
- (3) whether project on schedule and whether funding adequate to complete the program;
- (4) work plan for the coming month;
- (5) recommendations, if any, for desirable specification changes;
- (6) a reliability analysis;
- (7) a complete failure analysis;
- (8) radiation effects analysis;
- (9) complete design information and drawings for any test jigs used in testing the unit;
- (10) test procedures.

5. Preparation for Delivery

5.1 General

Equipment prepared for delivery shall be packaged in manner to ensure delivery without damage. It shall be enclosed by a vapor barrier, which shall contain a desiccant. The humidity state shall be ascertainable without breakage of the vapor seal. The packaging shall also be suitable for storage. The package and equipment shall survive a temperature range (non-operating) of -30°C to +70°C.

5.2 Shipping Instructions

The F. O. B. destination shall be Goddard Space Flight Center, Greenbelt, Maryland. Packages shall be marked as follows:

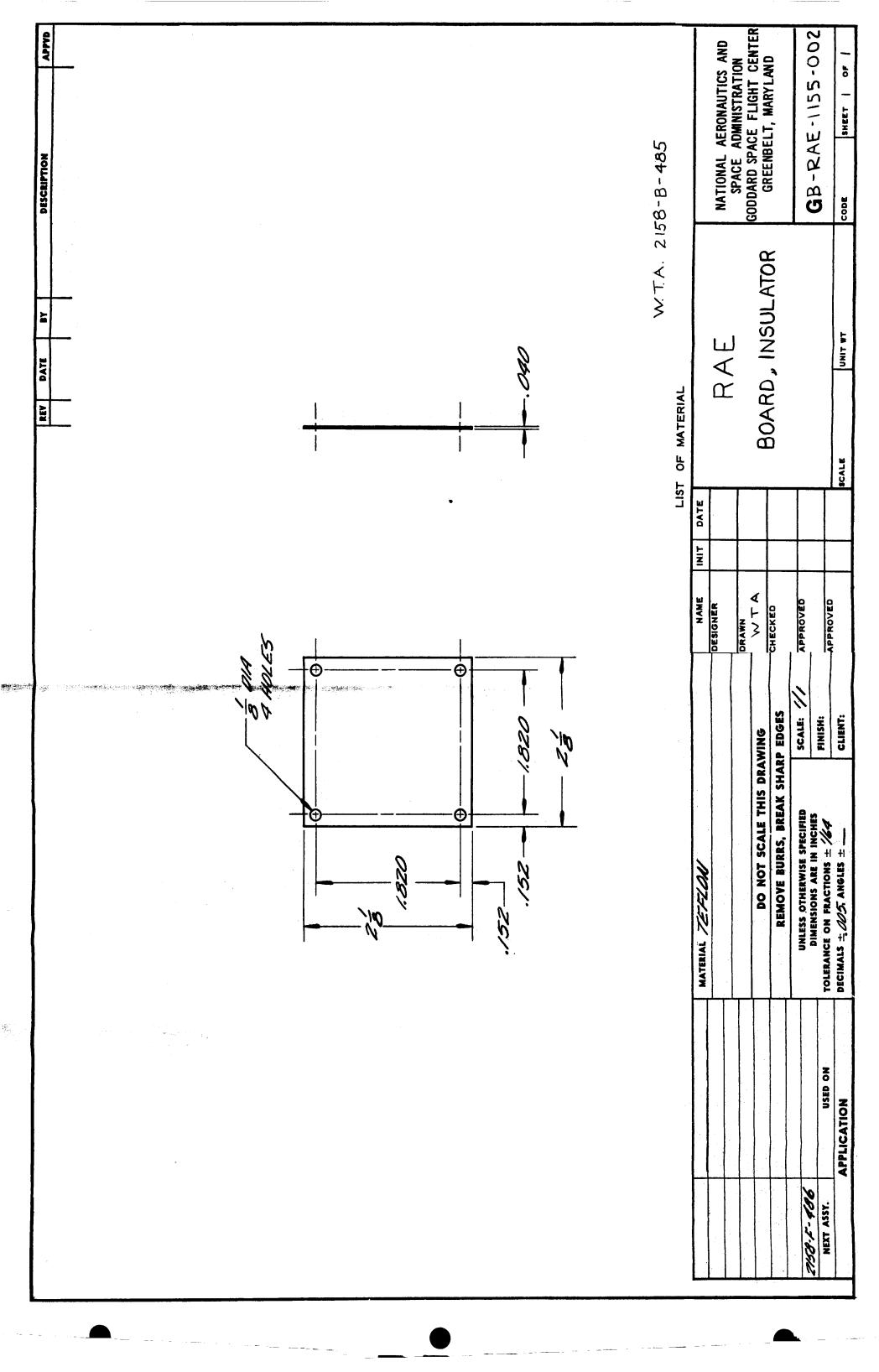
National Aeronautics and Space Administration Goddard Space Flight Center

Code 615

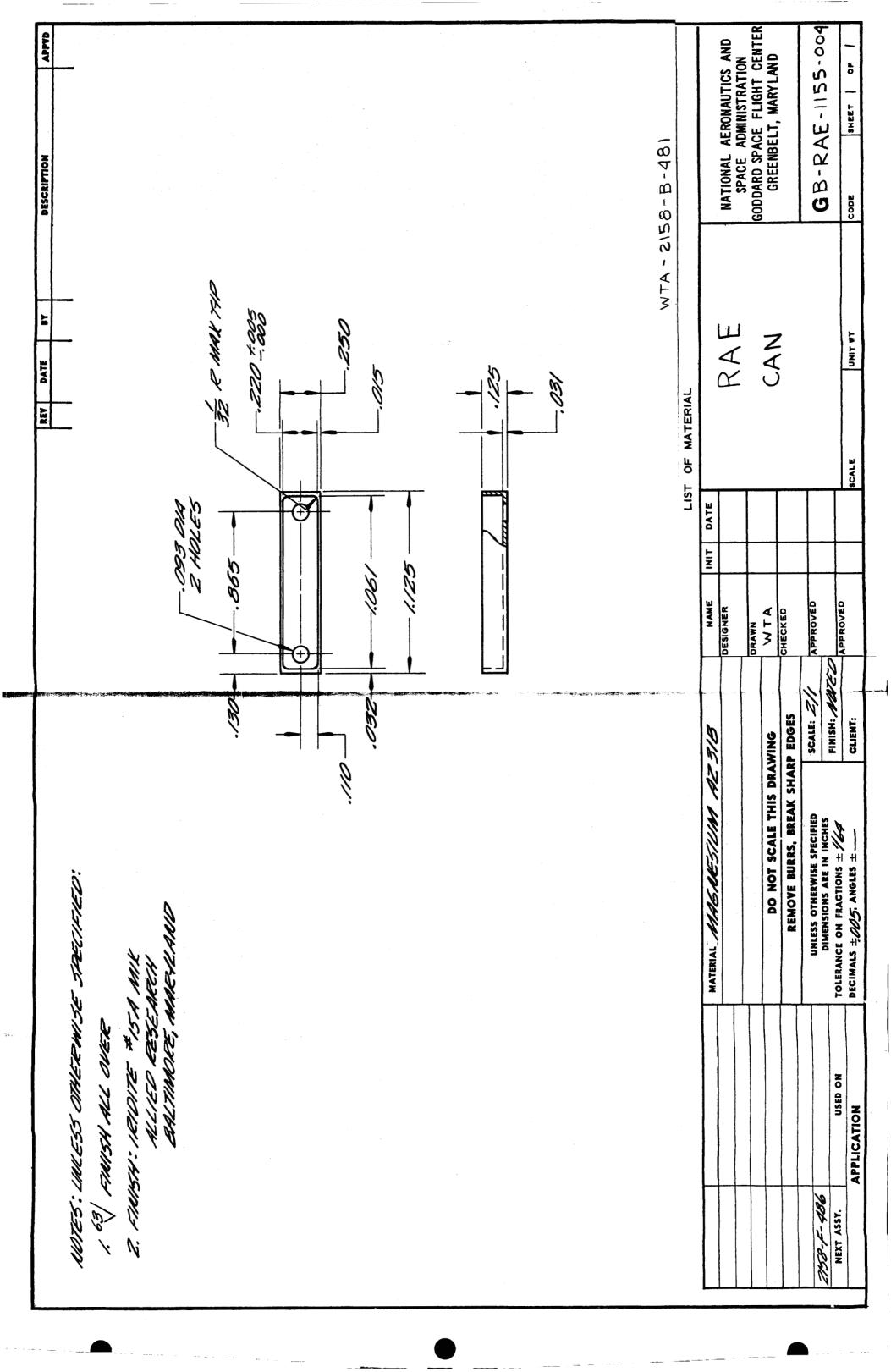
Greenbelt, Maryland 20771
Attention: Dr. R. G. Stone
HANDLE WITH EXTREME CAUTION

Completed hardware shall be packaged as specified by level C of FED-STD-102.

NATIONAL AERONAUTICS AND SPACE ADMINISTRATION GODDARD SPACE FLIGHT CENTER GREENBELT, MARYLAND GB-RAE-1155.001 UNIT WT. **P** WTA - 2158.8-483 MATL SPEC DESCRIPTION CODE STANDOFF MATL RAE ¥ TW LIND DATE LIST OF MATERIAL REV SCALE DATE DESCRIPTION HIN X T X NAME **NPPROVED** APPROVED DESIGNER CHECKED DRAWN FINISH: NOTED SCALE: 4// REMOYE BURRS, BREAK SHARP EDGES CLIENT: DO NOT SCALE THIS DRAWING MATERIAL CAR'S 303 NOTES: UNLESS OTHERWISE SPECIFIED 1.63 FINISH ALL ONER USED ON APPLICATION 3158-7-406 NEXT ASSY.



NATIONAL AERONAUTICS AND SPACE ADMINISTRATION GODDARD SPACE FLIGHT CENTER GREENBELT, MARYLAND APPVD GB-RAE-1155-003 -DESCRIPTION CODE W.T.A. 2158-B-484 UNIT WT SPACER RAE DATE LIST OF MATERIAL SCALE DATE FIN NAME APPROVED APPROVED DRAWN DESIGNER CHECKED FINISH: NOTED SCALE: 4// DO NOT SCALE THIS DRAWING REMOVE BURRS, BREAK SHARP EDGES CLIENT: 11/10 UNLESS OTHERWISE SPECIFIED DIMENSIONS ARE IN INCHES TOLERANCE ON FRACTIONS $\pm \% \phi$ DECIMALS $\pm M \mathcal{S}$, ANGLES \pm NOTES: UNILESS OTHERWISE SPECIFIED: MATERIAL BROYSS USED ON APPLICATION 3158-5-486 NEXT ASSY.



Encapsulation Procedure Ä.

- Trim all modules to dimensions shown on individual welded module drawings
- Load Header, (top A layer film with module output lead locations triangles punched), leaving headers at least 1/4 inch larger on all sides than the welded module. S.
- header punching C. for proper loading and Ġ <u>ო</u>
- or equivalent, using a strip of styrafoam for backing (See Figure 1). Insert welded module leads through a 1/16" thick strip of RTV-11 4.
- 70° 80°C oven for at least 15 minutes Preheat welded modules in a . م
- C-7--see Preparation of Epoxy) to bridge all components and to run The amount of epoxy to be used since the modules cool rapidly upon epoxy should be applied with Walsco Electronics No. 987 Chem-O-Conformal coat welded modules with sufficient epoxy (Armstrong Jector, or equivalent. It should be noted that the epoxy should be is proportional to the component density of the module.) The (Note: exposure to room temperature. applied as quickly as possible between all layers of film. 9
- is will allow excess epoxy to run Return modules to oven and heat at 70° - 80°C for 15 minutes les are in a horizontal position (Caution: Make sure modu as shown in Figure 2. off modules. ۲.

the modules in the oven for an additional Then turn over the module holding device, such that the module top (Note: At this point any excess epoxy may be wiped from the surface of the modules with a in Figure 2 is now in the bottom position. small mixing splint). Leave 15 minutes.

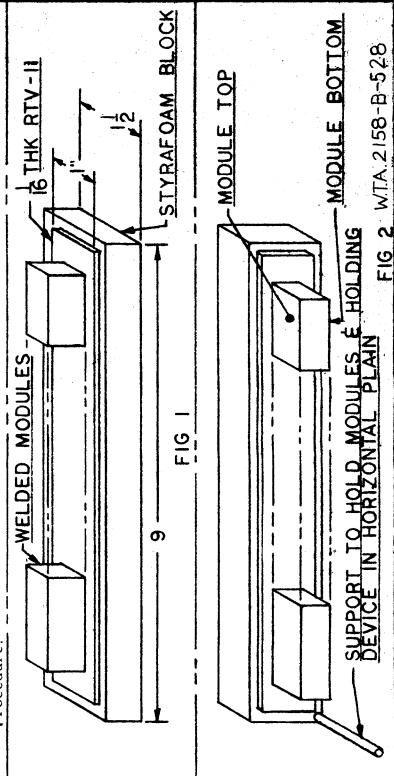
strip and styrafoam backing material. After removal from the RTV-11 strip, trim the headers to size as indicated on the individual welded oven and let cool at room temperature emoving the modules from the RTV-11 Remove the modules from the for 4 or more hours before re module drawings. ω.

Epoxy
of
Preparation
Prep
Β.

- Materials
- Armstrong Epoxy Resin Products (C-7) resin
- Armstrong Epoxy Resin Products activator (W) Ъ.
- Mixture $^{\circ}$
- 35 grams
- -15 grams Activator W ۵,

e., 7 to 3 parts by weight (Pbw) Resin to Activator respectively to allow for minimum outgassing requirements of the epoxy).

Then The epoxy is now ready for Step (6) of Encapsulation Mix the resin and activator thoroughly for at least 5 minutes, then set aside for 15 minutes at room temperature to allow the tranped air Intervals. bubbles to rise to the surface. Stir lightly at 5 minute fill the syringe. **Procedure**. €.



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				DIMENSIONS ARE IN INCHES		
		APPROVED	Scalii S	UNLESS OTHERWISE SPECIFIED		
	1					
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		H - N		DO NOT SCALE THIS DRAWING		
		DRAWN				
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		DESIGNER				
•	- - - - -	NAME	. ,!	MATERIAL		_
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GODDARD SPACE FLIGHT CENTER GREENBELT, MARYLAND

ENCAPSULATION

RAE

DATE

PROCEDURE

NATIONAL AERONAUTICS AND

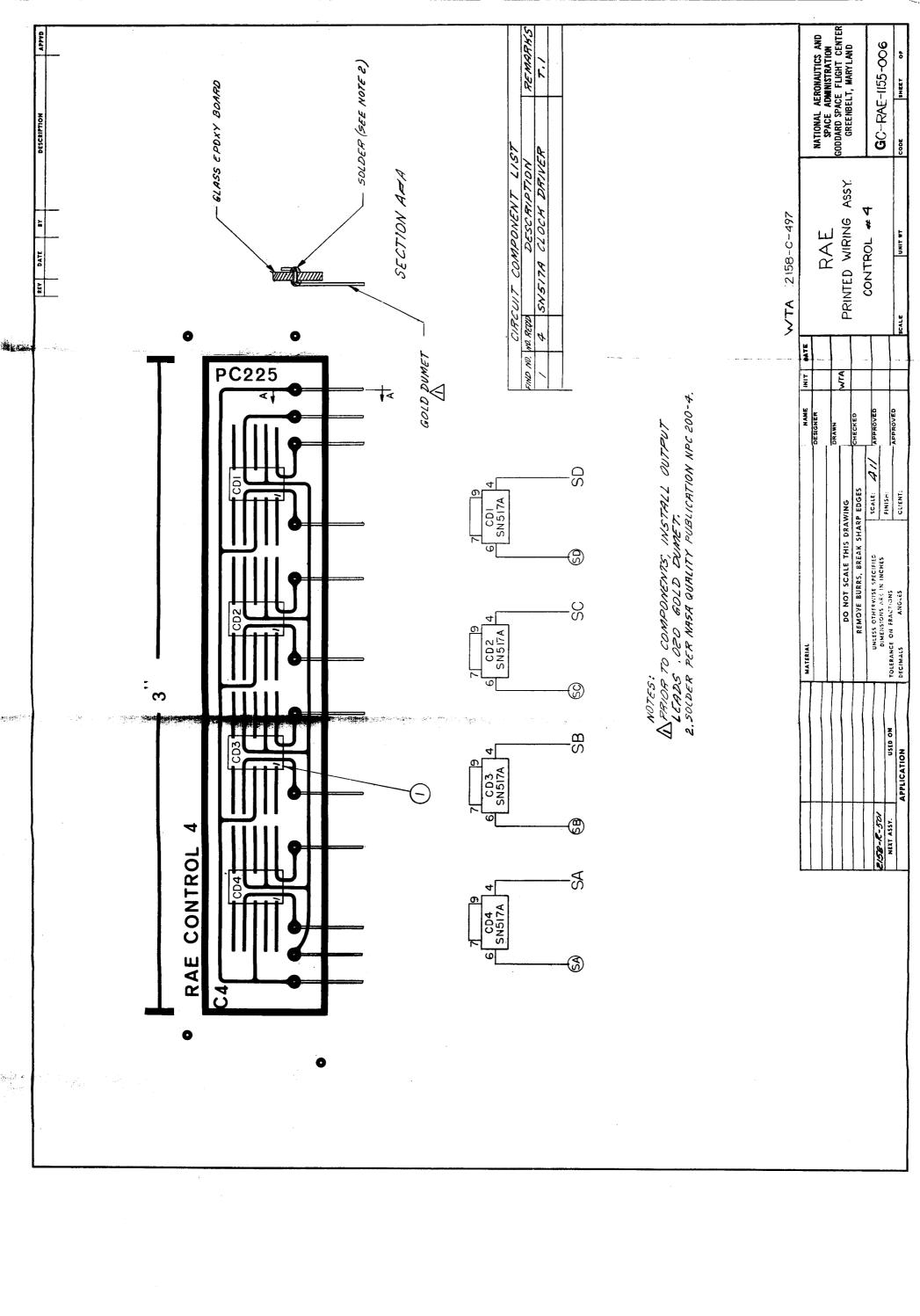
SPACE ADMINISTRATION

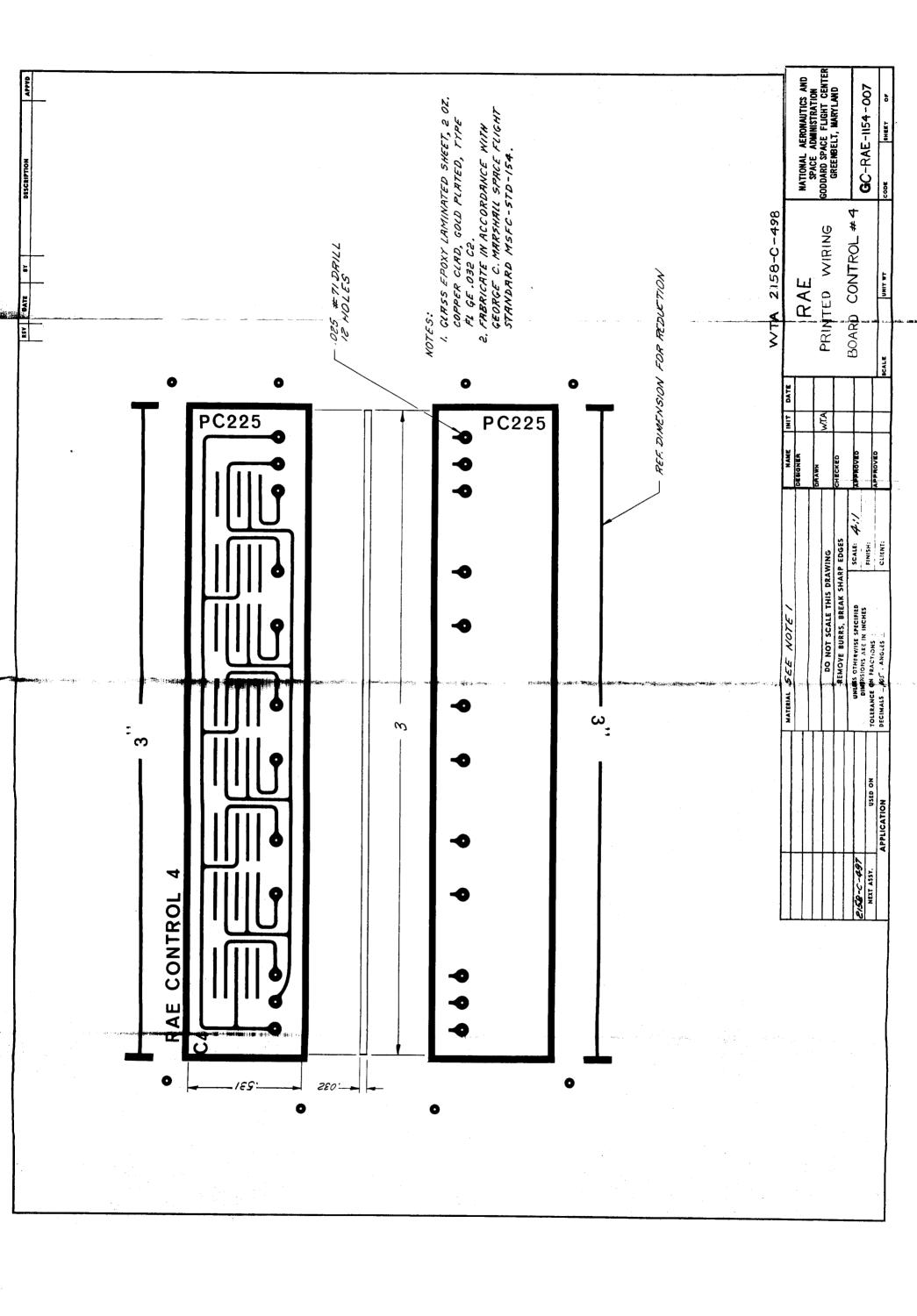
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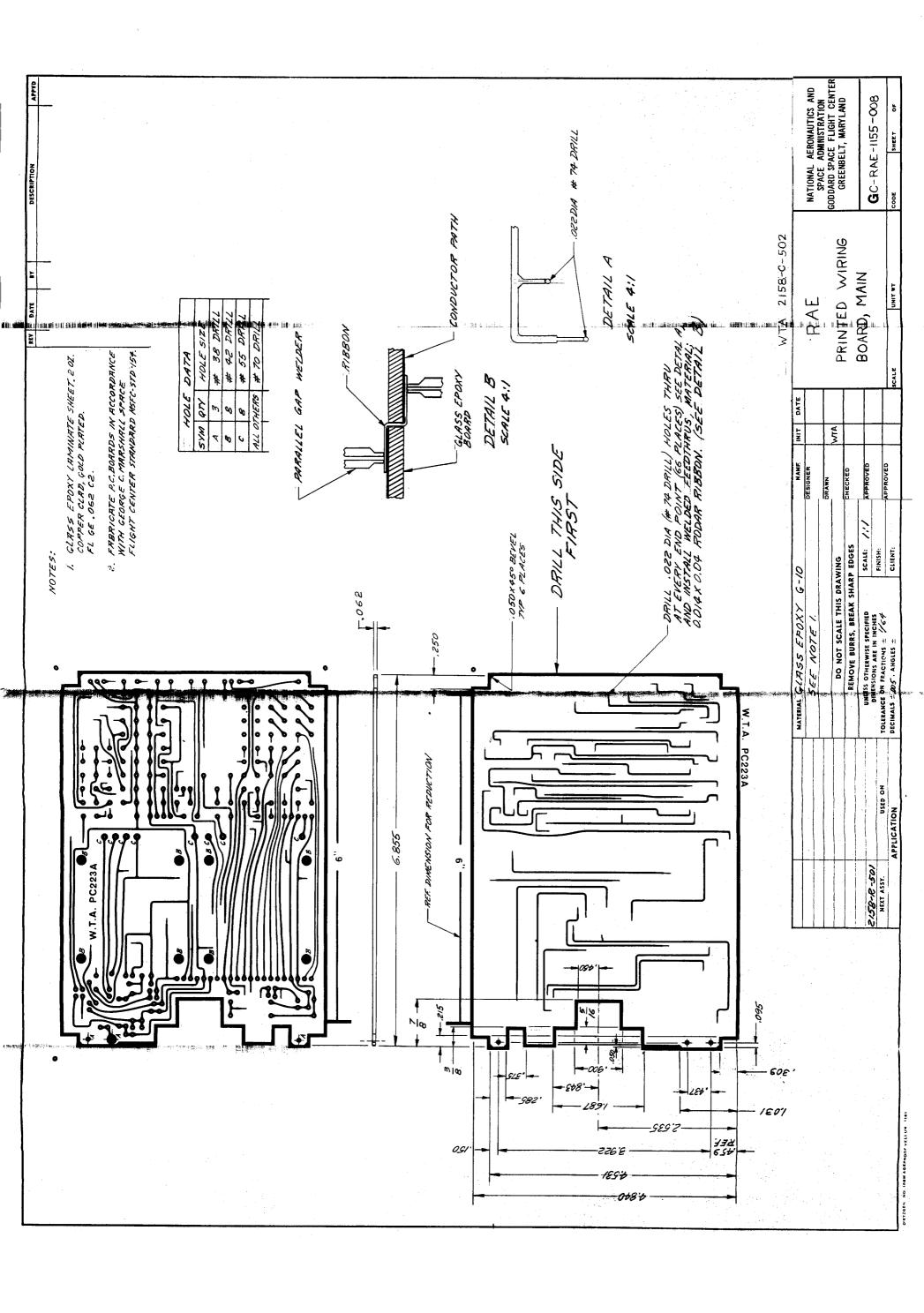
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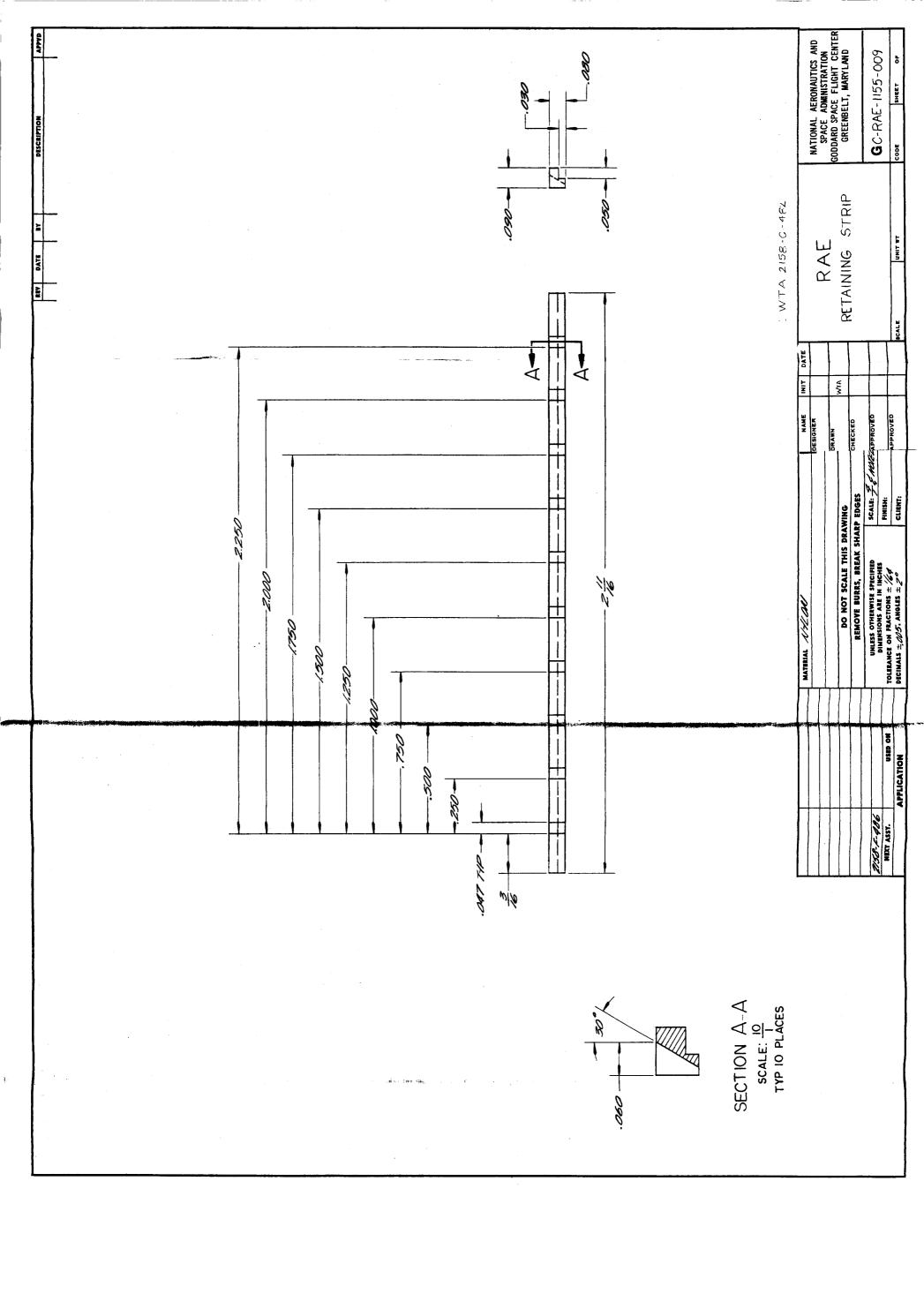
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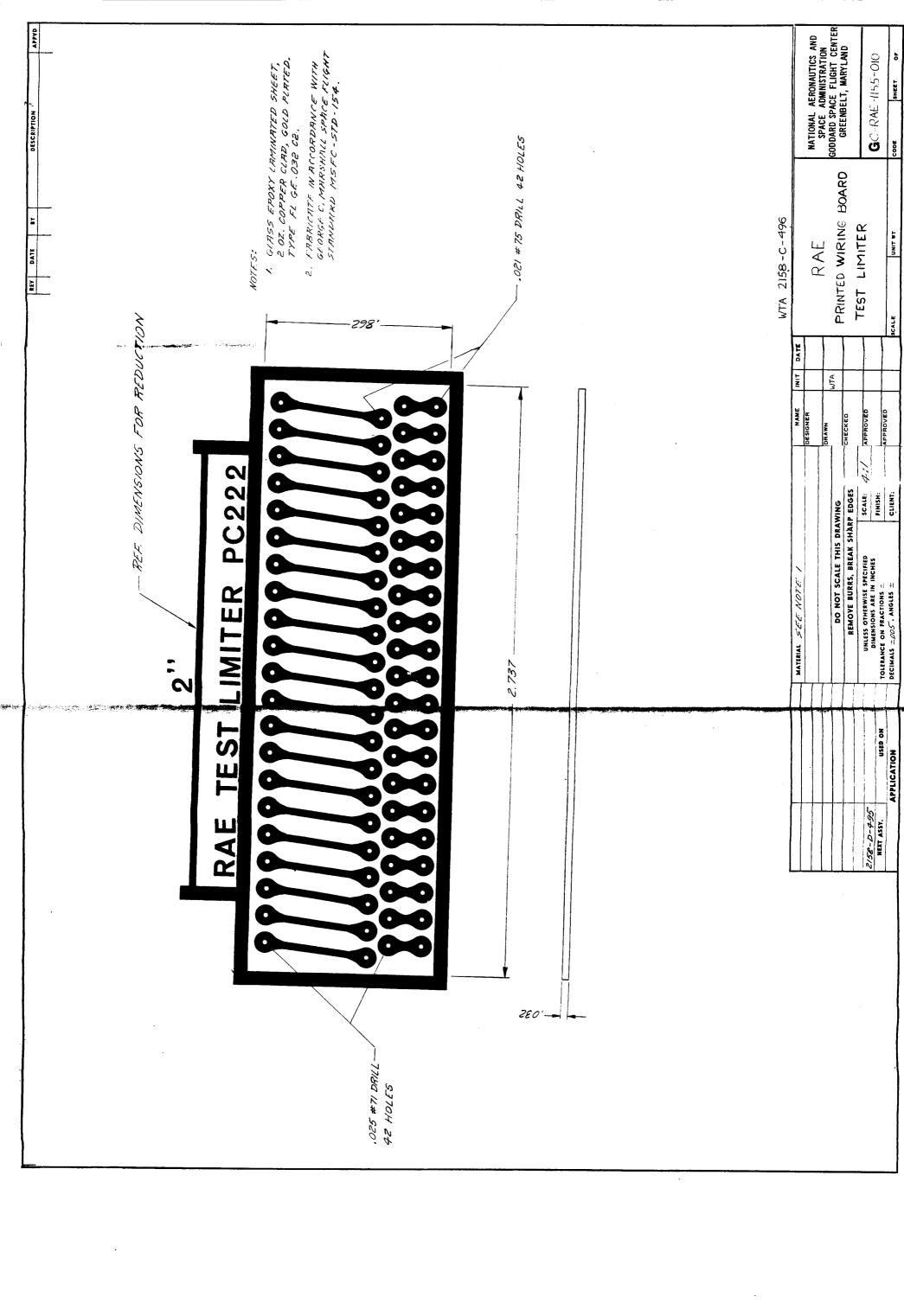
DRITHER NO. 1981 ASTPROOF VELLUM 1161

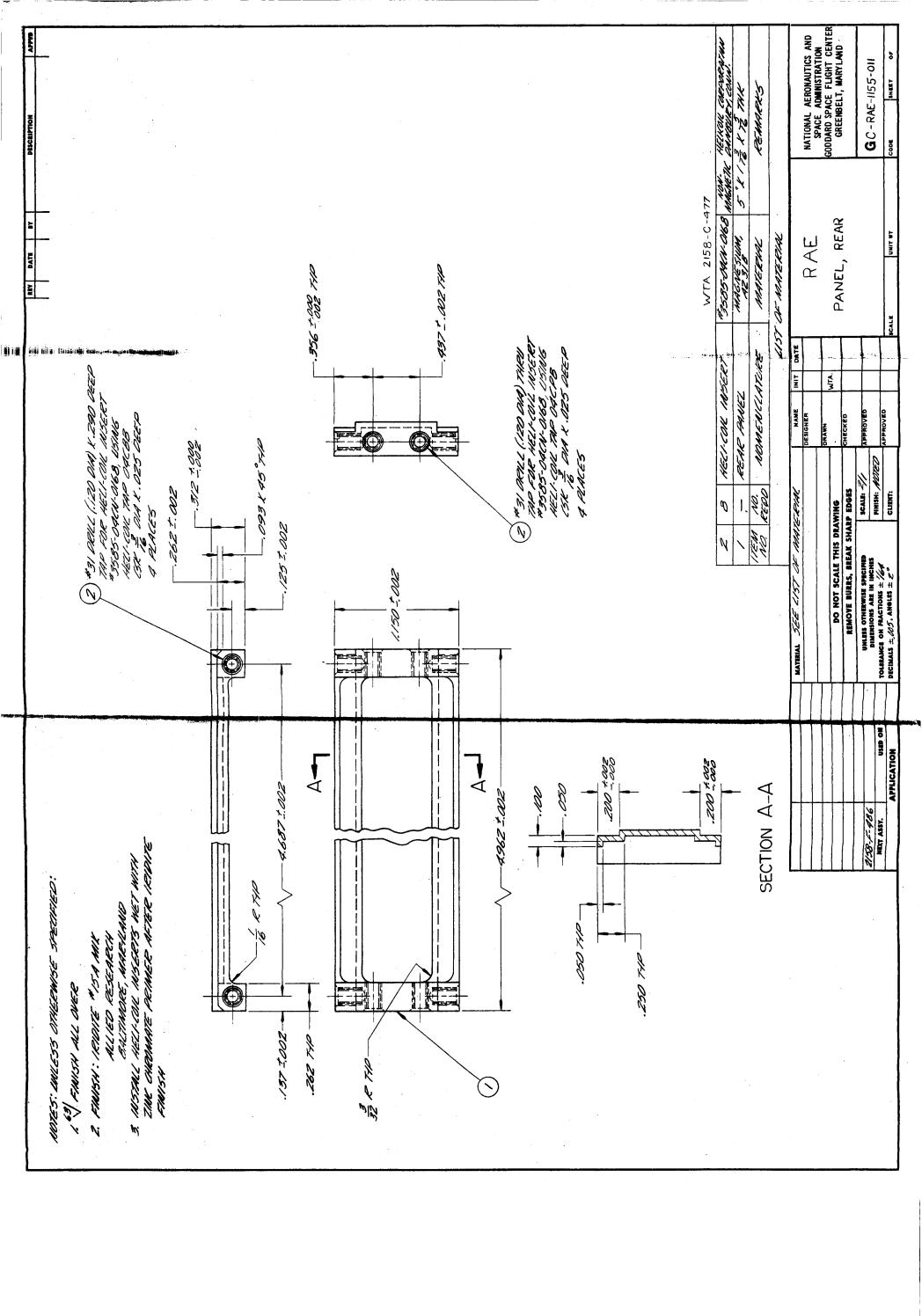


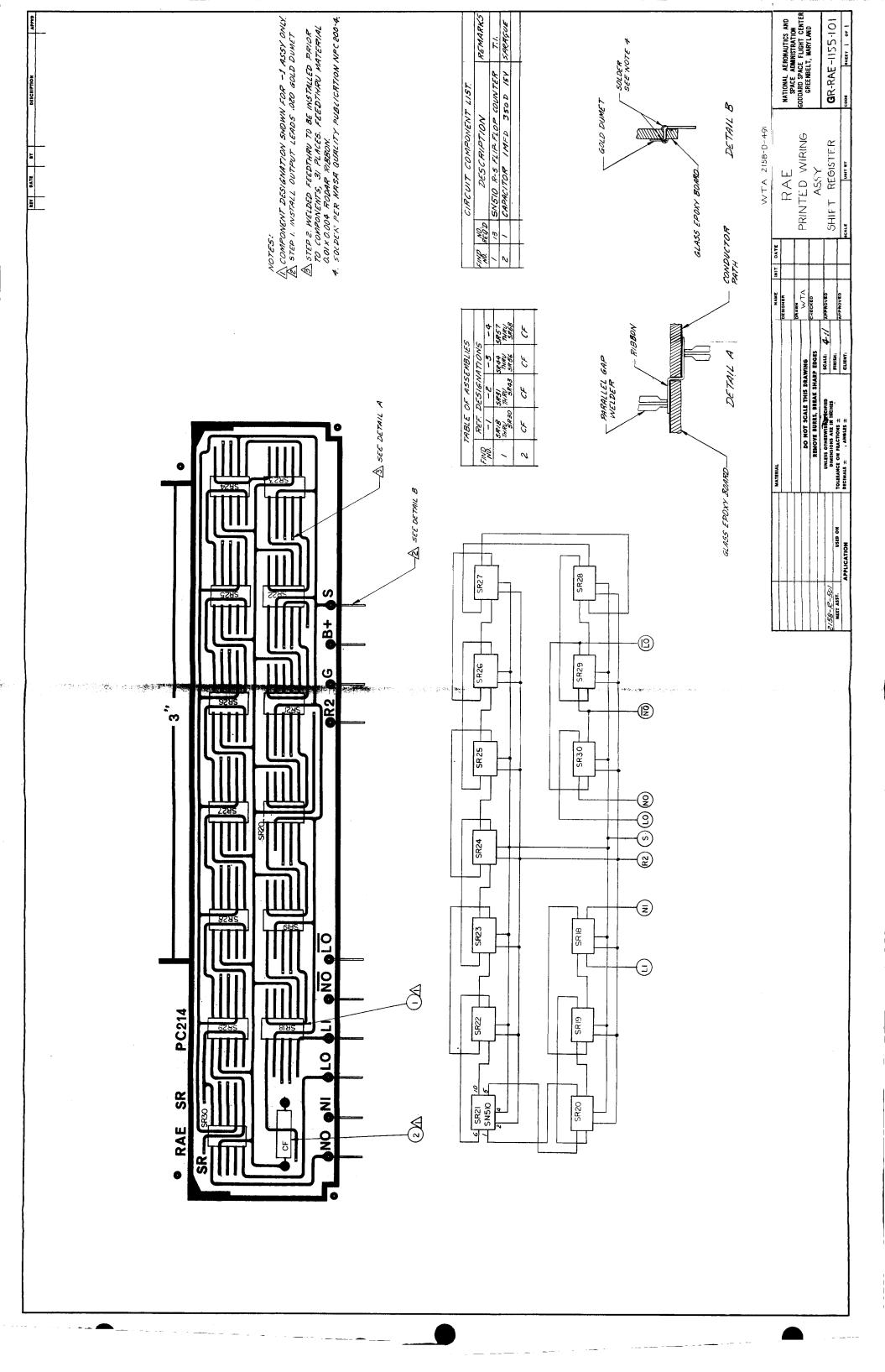


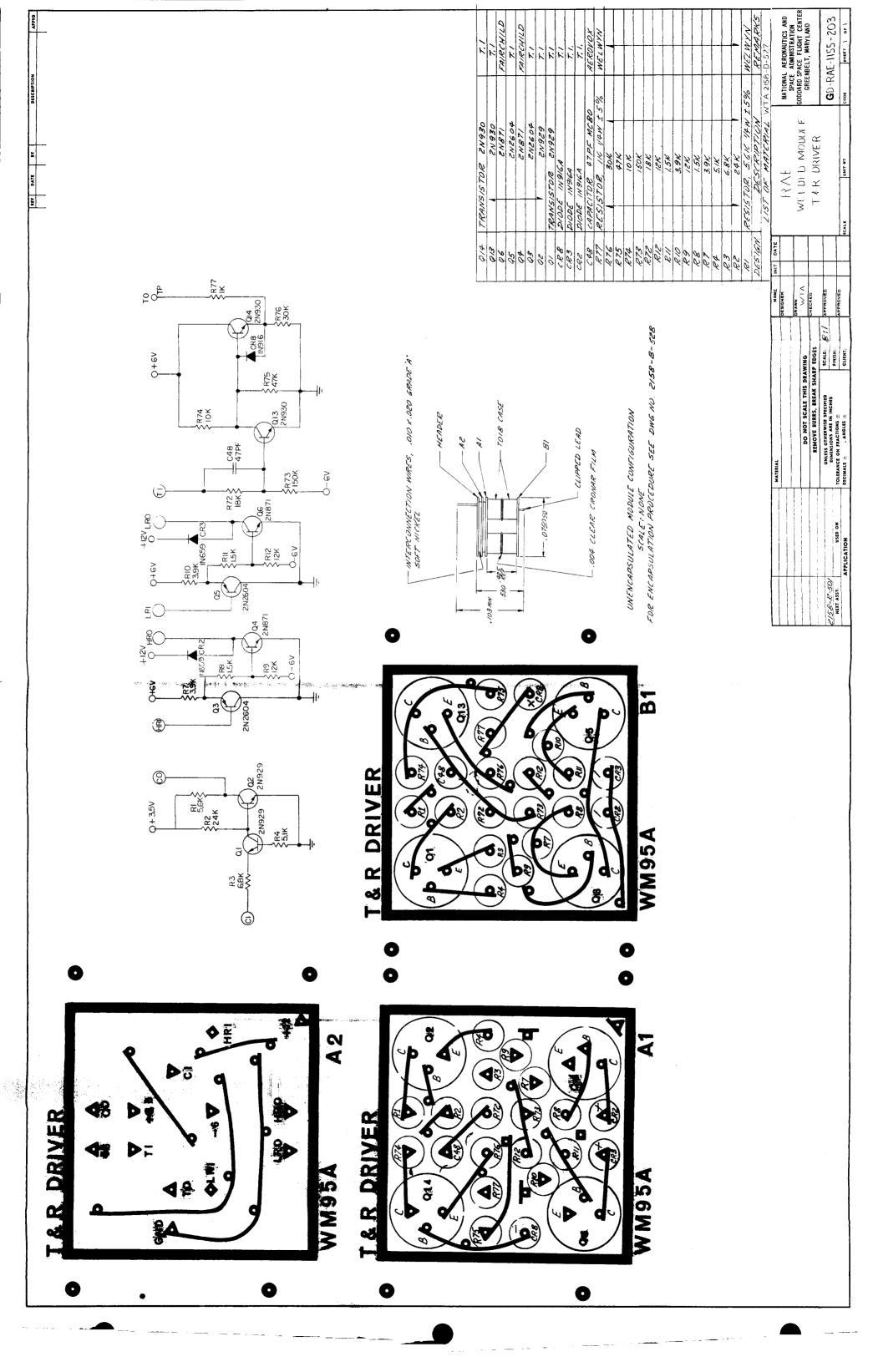


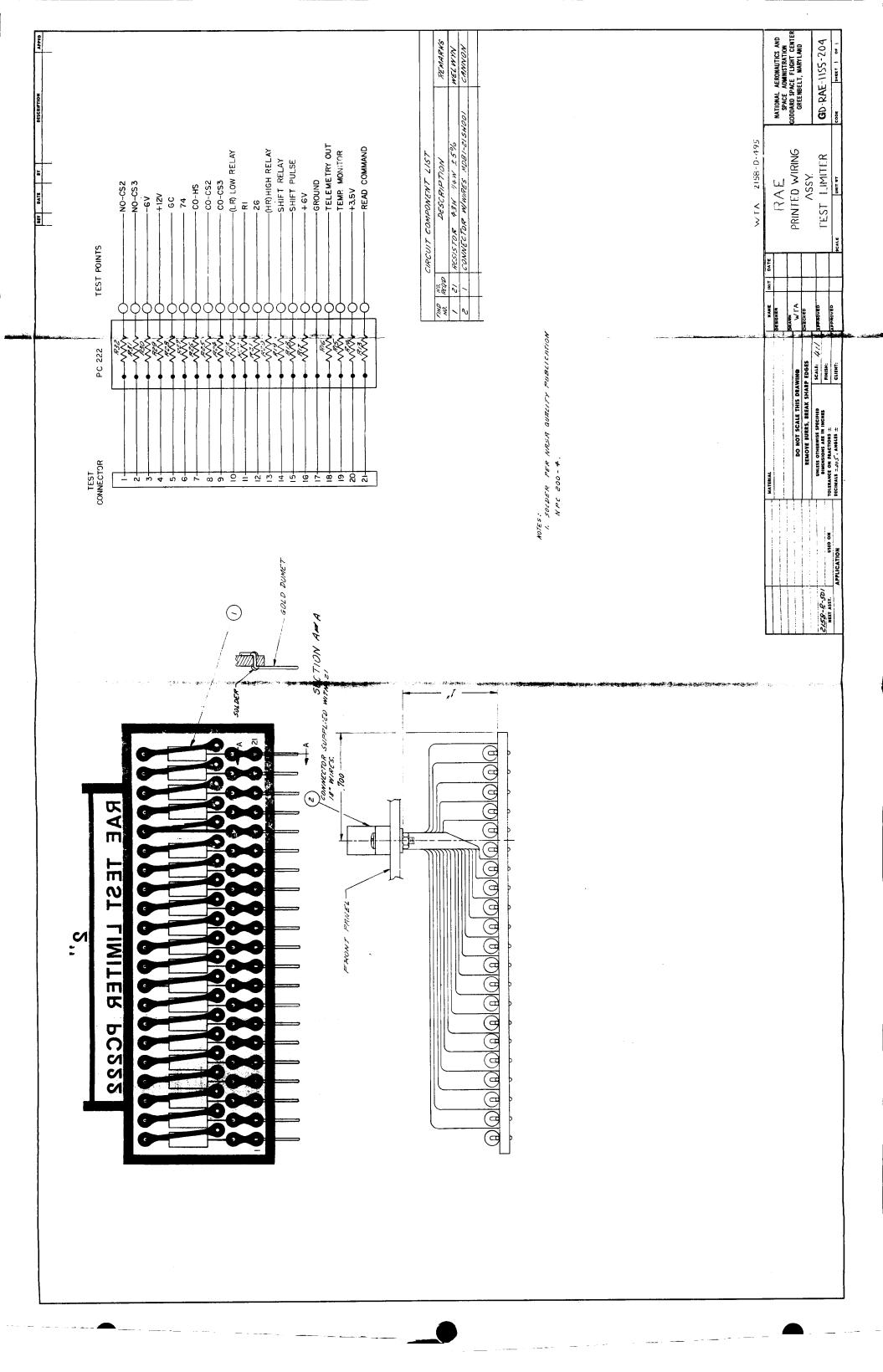


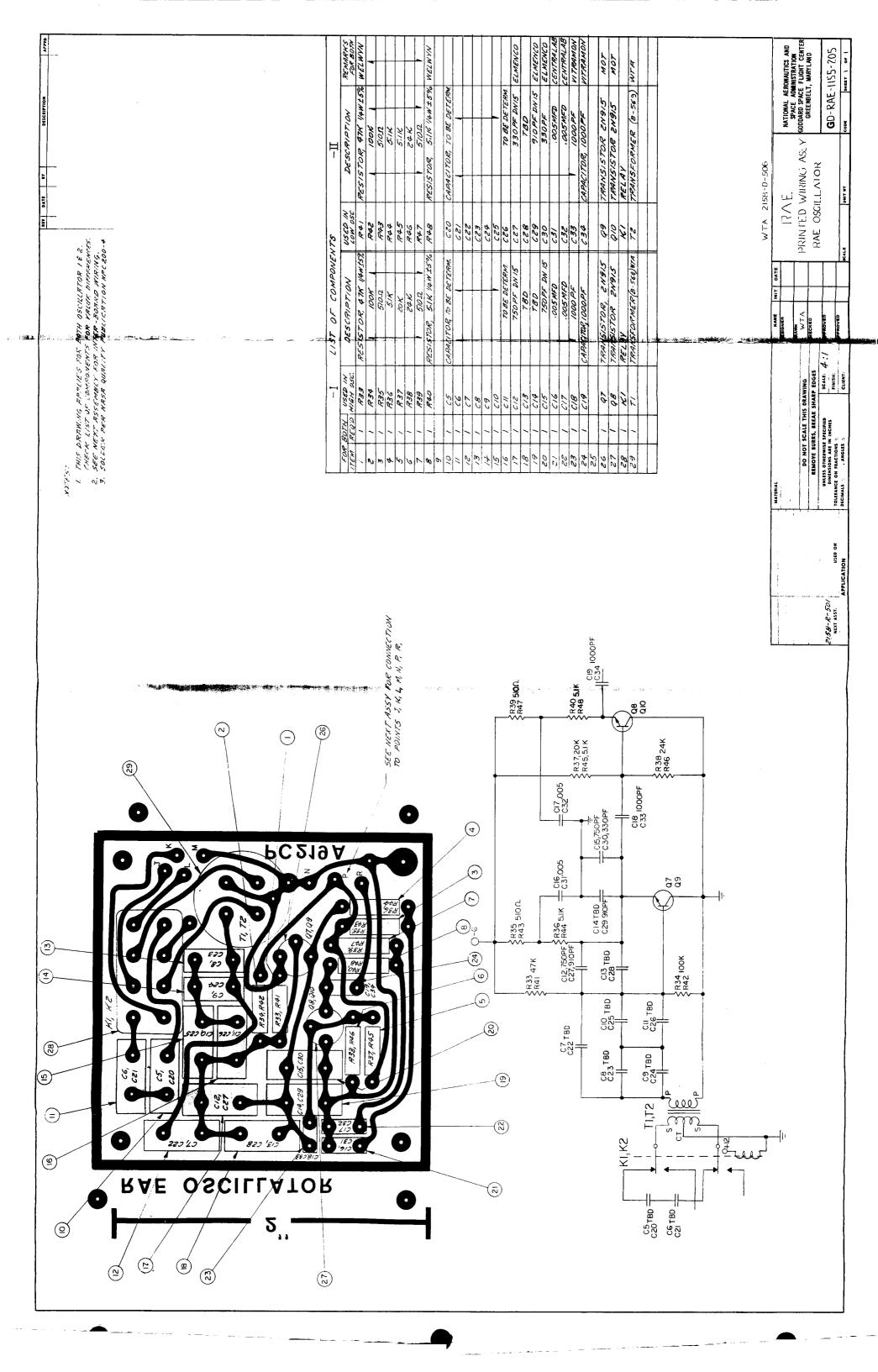


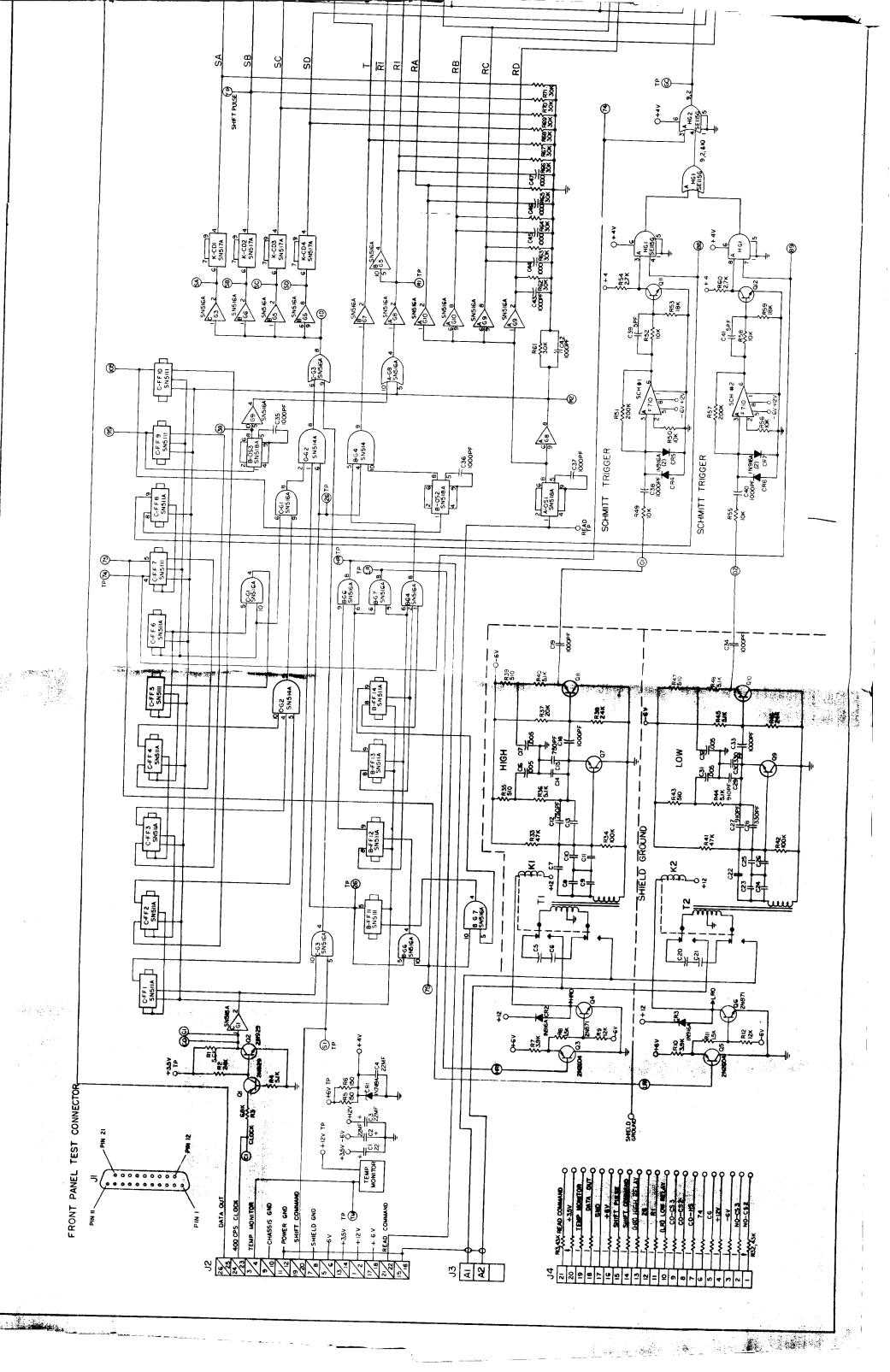


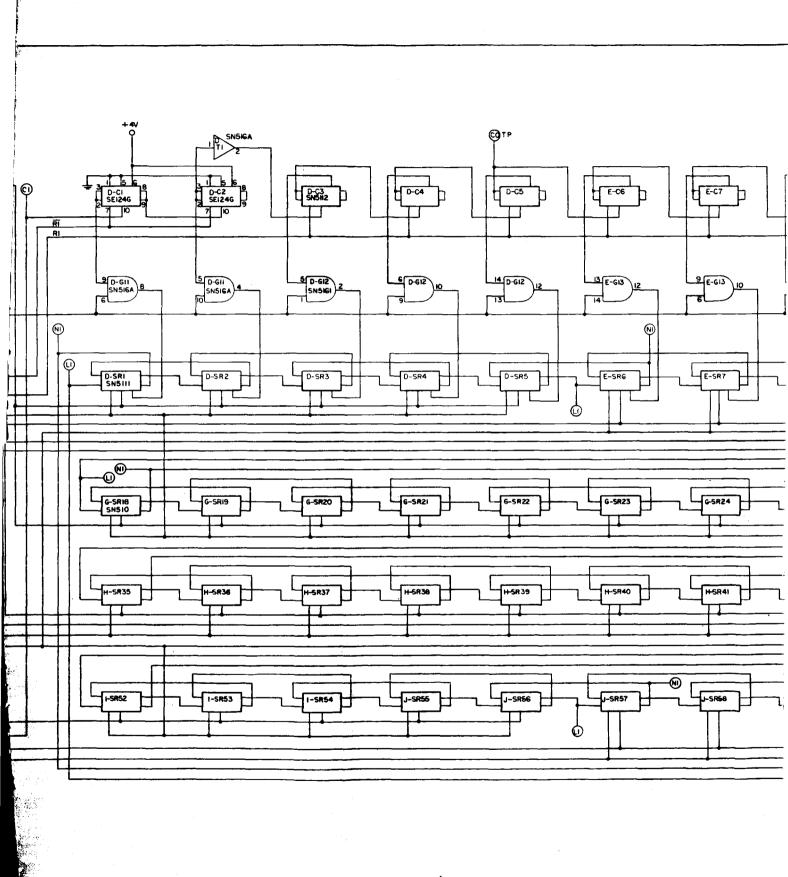












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